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MOS INTEGRATED CIRCUIT

___ 78011F, 78012F, 78013F, 78014F, 78015F, 78016F, 78018F

8-BIT SINGLE-CHIP MICROCONTROLLER



★ DESCRIPTION

The μ PD78011F, 78012F, 78013F, 78014F, 78015F, 78016F, and 78018F are the products in the μ PD78018F subseries within the 78K/0 series.

Compared with the older μ PD78014 subseries, this subseries operates at lower voltage and provides a fuller set of ROM and RAM variations.

A one-time PROM or EPROM product μ PD78P018F capable of operating in the same power supply voltage range as of the mask ROM product and other development tools are also provided.

Functions are described in detail in the following User's Manual, which should be read when carring out design work.

 μ PD78018F, 78018FY Subseries User's Manual: U10659E 78K/0 Series Users Manual – Instruction : U12326E

FEATURES

· Large on-chip ROM & RAM

Item	Program		Data Memory		
	Memory	Internal High-	Internal	Buffer RAM	Package
Product Name	(ROM)	Speed RAM	Expanded RAM	Bullet KAW	
μPD78011F	8K bytes	512 bytes	_	32 bytes	64-pin plastic shrink DIP (750 mil)
μPD78012F	16K bytes				64-pin plastic QFP (14 × 14 mm)
μPD78013F	24K bytes	1024 bytes			64-pin plastic LQFP (12 × 12 mm)
μPD78014F	32K bytes				
μPD78015F	40K bytes		512 bytes		
μPD78016F	48K bytes				
μPD78018F	60K bytes		1024 bytes		

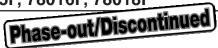
- External memory expansion space : 64K bytes
- I/O ports: 53 (N-ch open-drain: 4)
- 8-bit resolution A/D converter: 8 channels
- · Serial interface : 2 channels
- Timer: 5 channels
- Supply voltage : VDD = 1.8 to 5.5 V

APPLICATION FIELDS

Cellular phone, pager, VCR, audio, camera, home appliances, etc

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ORDERING INFORMATION

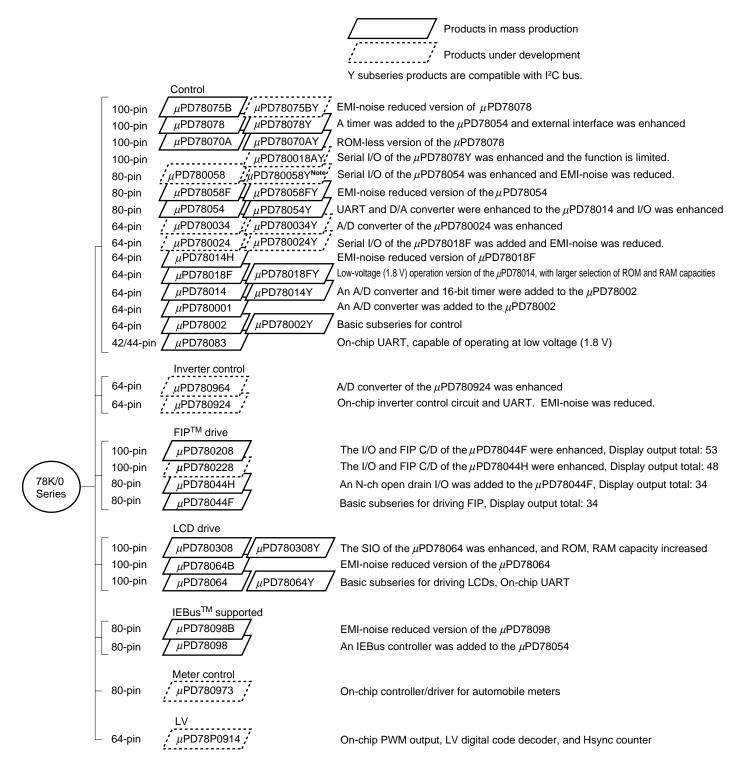
Part Number	Package
μPD78011FCW-×××	64-pin plastic shrink DIP (750 mil)
μ PD78011FGC- \times \times -AB8	64-pin plastic QFP (14 × 14 mm)
μ PD78011FGK- \times \times -8A8	64-pin plastic LQFP (12 × 12 mm)
μ PD78012FCW- $\times\!\times\!$	64-pin plastic shrink DIP (750 mil)
μ PD78012FGC-×××-AB8	64-pin plastic QFP (14 × 14 mm)
μ PD78012FGK- \times \times -8A8	64-pin plastic LQFP (12 × 12 mm)
μ PD78013FCW- $\times\!\times\!$	64-pin plastic shrink DIP (750 mil)
μ PD78013FGC-×××-AB8	64-pin plastic QFP (14 × 14 mm)
μ PD78013FGK- \times \times -8A8	64-pin plastic LQFP (12 × 12 mm)
μ PD78014FCW- $\times\!\times\!$	64-pin plastic shrink DIP (750 mil)
μ PD78014FGC-×××-AB8	64-pin plastic QFP (14 × 14 mm)
μ PD78014FGK-×××-8A8	64-pin plastic LQFP (12 × 12 mm)
μ PD78015FCW- $\times\!\times\!$	64-pin plastic shrink DIP (750 mil)
μ PD78015FGC-×××-AB8	64-pin plastic QFP (14 × 14 mm)
μ PD78015FGK-×××-8A8	64-pin plastic LQFP (12 × 12 mm)
μ PD78016FCW- $\times\!\times\!$	64-pin plastic shrink DIP (750 mil)
μ PD78016FGC-×××-AB8	64-pin plastic QFP (14 × 14 mm)
μ PD78016FGK-×××-8A8	64-pin plastic LQFP (12 × 12 mm)
★ μPD78018FCW-×××	64-pin plastic shrink DIP (750 mil)
★ μPD78018FGC-×××-AB8	64-pin plastic QFP (14 × 14 mm)
★ μPD78018FGK-×××-8A8	64-pin plastic LQFP (12 × 12 mm)





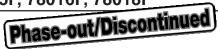
★ 78K/0 SERIES DEVELOPMENT

The following shows the products organized according to usage. The names in the parallelograms are subseries names.



Note Under planning





The following lists the main functional differences between subseries products.

	Function	ROM		Tin	ner		8-bit	10-bit	8-bit	Serial Interface	I/O	V _{DD} MIN.	External
Subseries	Name	Capacity	8-bit	16-bit	Watch	WDT	A/D	A/D	D/A	Senai interrace	1/0	Value	Expansion
Control	μPD78075B	32K-40K	4ch	1ch	1ch	1ch	8ch	_	2ch	3ch (UART: 1ch)	88	1.8 V	0
	μPD78078	48K-60K											
	μPD78070A	_									61	2.7 V	
	μPD780058	24K-60K	2ch						2ch	3ch (time division UART: 1ch)	68	1.8 V	
	μPD78058F	48K-60K								3ch (UART: 1ch)	69	2.7 V	
	μPD78054	16K-60K										2.0 V	
	μPD780034	8K-32K					_	8ch	_	3ch (UART: 1ch,	51	1.8 V	1
	μPD780024						8ch	-		time division 3-wire: 1ch)			
	μPD78014H									2ch	53	1.8 V	
	μPD78018F	8K-60K											
	μPD78014	8K-32K										2.7 V	1
	μPD780001	8K		_	_					1ch	39		_
	μPD78002	8K-16K			1ch		_				53		0
	μPD78083				-		8ch			1ch (UART: 1ch)	33	1.8 V	_
Inverter	μPD780964	8K-32K	3ch	Note	_	1ch	_	8ch	_	2ch (UART: 2ch)	47	2.7 V	0
control	μPD780924						8ch	1					
FIP	μPD780208	32K-60K	2ch	1ch	1ch	1ch	8ch	-	_	2ch	74	2.7 V	-
drive	μPD780228	48K-60K	3ch	_	_					1ch	72	4.5 V	
	μPD78044H	32K-48K	2ch	1ch	1ch						68	2.7 V	
	μPD78044F	16K-40K								2ch			
LCD	μPD780308	48K-60K	2ch	1ch	1ch	1ch	8ch	_	_	3ch (time division UART: 1ch)	57	2.0 V	-
drive	μPD78064B	32K								2ch (UART: 1ch)			
	μPD78064	16K-32K											
IEBus	μPD78098	40K-60K	2ch	1ch	1ch	1ch	8ch	-	2ch	3ch (UART: 1ch)	69	2.7 V	0
supported	μPD78098B	32K-60K											
Meter control	μPD780973	24K-32K	3ch	1ch	1ch	1ch	5ch	-	_	2ch (UART: 1ch)	56	4.5 V	_
LV	μPD78P0914	32K	6ch	_	_	1ch	8ch	_	_	2ch	54	4.5 V	0

Note 10-bit timer: 1 channel





OVERVIEW OF FUNCTION (1/2)

*	
_	

Item Product Name		μPD78011F	μPD78012F	μPD78013F	μPD78014F	μPD78015F	μPD78016F	μPD78018F		
	ROM	8K bytes	16K bytes	24K bytes	32K bytes	40K bytes	48K bytes	60K bytes		
Internal	High-speed RAM	51	2 bytes	,		1024 byte				
memory	Expanded RAM		_	_		512 1	oytes	1024 bytes		
	Buffer RAM	32 bytes								
Memory sp	ace	64K bytes								
General-pu	rpose registers	8 bits × 32 re	gisters (8 bits	× 8 registers ×	4 banks)					
Minimum ins	truction execution time	On-chip minii	mum instructio	n execution tin	ne cycle modifi	cation function				
	nen main system ock selected	0.4 μs/0.8 μs	/1.6 μs/3.2 μs/	/6.4 μs (at 10.0	MHz operatio	n)				
	nen subsystem ock selected	122 μs (at 32	.768 kHz oper	ation)						
Instruction	set		on/division (8 b ation (set, rese	oits × 8 bits,16 et, test, boolea						
I/O ports			t open-drain I/O tand voltage)	: 53 : 2 : 47						
A/D conver	ter	 8-bit resolution × 8 channels Operable over a wide power supply voltage range: AV_{DD} = 1.8 to 5.5 V 								
Serial inter	face	3-wire serial I/O/SBI/2-wire serial I/O mode selectable: 1 channel 3-wire mode (on-chip max. 32 bytes automatic data transmit/receive function): 1 channel								
Timer		16-bit timer/event counter : 1 channel 8-bit timer/event counter : 2 channels Watch timer : 1 channel Watchdog timer : 1 channel								
Timer outp	ut	3 (14-bit PWM output × 1)								
Clock outpo	ut	39.1 kHz, 78.1 kHz, 156 kHz, 313 kHz, 625 kHz, 1.25 MHz (at main system clock: 10.0 MHz operation), 32.768 kHz (at subsystem clock: 32.768 kHz operation)								
Buzzer out	put	2.4 kHz, 4.9 kHz, 9.8 kHz (at main system clock: 10.0 MHz operation)								
Vectored interrupt										
sources Non-maskable Internal : 1										
	Software	1								





OVERVIEW OF FUNCTION (2/2)

Product Name	Item	μPD78011F	μPD78012F	μPD78013F	μPD78014F	μPD78015F	μPD78016F	μPD78018F	
Test input			Internal : 1 External : 1						
Supply voltage		V _{DD} = 1.8 to 5.5 V							
Operating ambient temperature		$T_A = -40 \text{ to } +85^{\circ}\text{C}$							
Package		• 64-pin plas	 64-pin plastic shrink DIP (750 mil) 64-pin plastic QFP (14 × 14 mm) 64-pin plastic LQFP (12 × 12 mm) 						





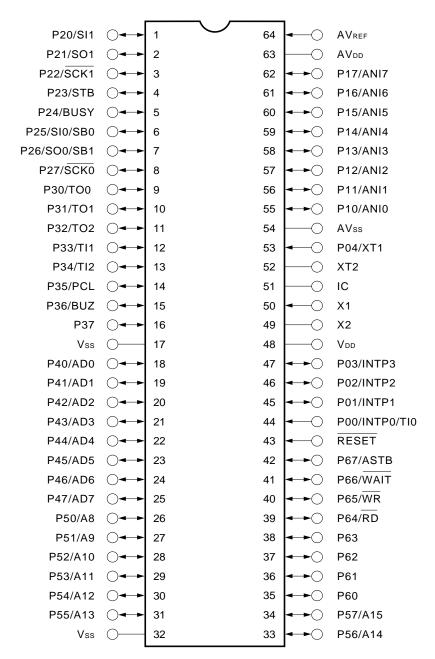
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- 1. PIN CONFIGURATION (Top View)



Cautions 1. Always connect the IC (Internally Connected) pin to Vss directly.

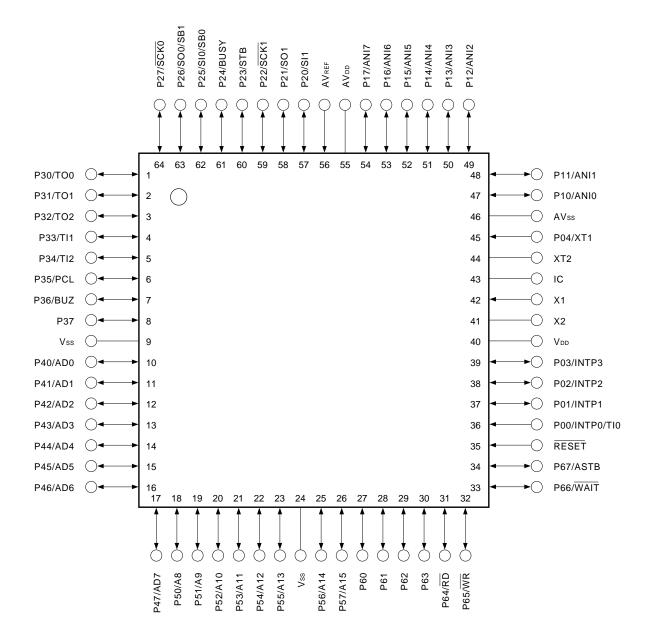
- 2. Always connect the AVDD pin to VDD.
- 3. Always connect the AVss pin to Vss.





- 64-Pin Plastic QFP (14 × 14 mm)
- **★** μPD78018FGC-××-AB8
 - 64-Pin Plastic LQFP (12 × 12 mm)

 - μ PD78014FGK-×××-8A8, 78015FGK-×××-8A8, 78016FGK-×××-8A8,
- **★** μPD78018FGK-×××-8A8



Cautions 1. Always connect the IC (Internally Connected) pin to Vss directly.

- 2. Always connect the AVDD pin to VDD.
- 3. Always connect the AVss pin to Vss.



Phase-out/Discontinued

A8 to A15 : Address Bus AD0 to AD7 : Address/Data Bus ANI0 to ANI7 : Analog Input **ASTB** : Address Strobe AV_{DD} : Analog Power Supply : Analog Reference Voltage **AV**REF

: Analog Ground **AVss**

BUSY : Busy

BUZ : Buzzer Clock

: Internally Connected IC INTP0 to INTP3: Interrupt from Peripherals

P00 to P04 : Port0 P10 to P17 : Port1 P20 to P27 : Port2 P30 to P37 : Port3

P40 to P47 : Port4 P50 to P57 : Port5 P60 to P67 : Port6

: Programmable Clock **PCL**

 $\overline{\mathsf{RD}}$: Read Strobe RESET : Reset SB0, SB1 : Serial Bus SCK0, SCK1 : Serial Clock SIO, SI1 : Serial Input SO0, SO1 : Serial Output

STB : Strobe : Timer Input TI0 to TI2 TO0 to TO2 : Timer Output : Power Supply V_{DD} Vss : Ground

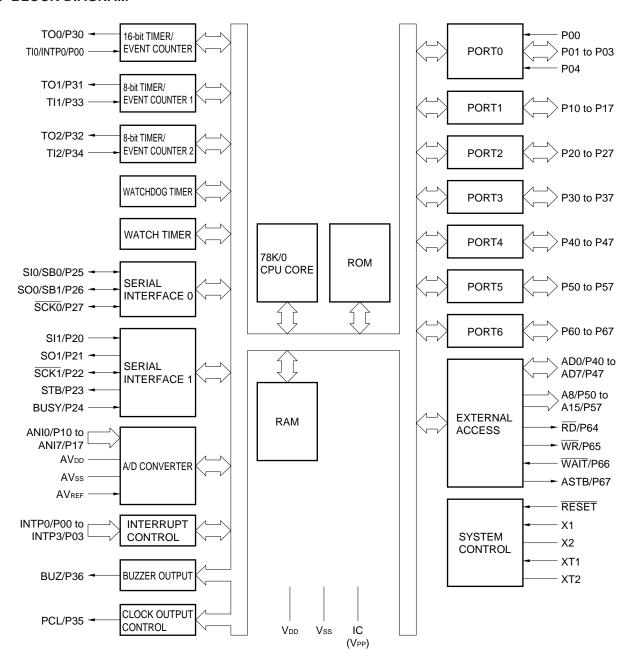
WAIT : Wait

WR : Write Strobe

X1, X2 : Crystal (Main System Clock) XT1, XT2 : Crystal (Subsystem Clock)



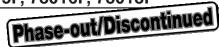
2. BLOCK DIAGRAM



Remarks 1. Internal ROM & RAM capacity varies depending on the product.

2. (): μ PD78P018F





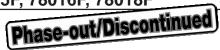
3. PIN FUNCTIONS

3.1 PORT PINS (1/2)

Pin Name	I/O		Function		Dual- Function Pin
P00	Input	Port 0	Input only	Input	INTP0/TI0
P01	Input/	5-bit I/O port	Input/output can be specified bit-wise.	Input	INTP1
P02	output		When used as an input port, on-chip pull-up resistor can be used in software.		INTP2
P03			resistor can be used in software.		INTP3
P04Note 1	Input		Input only	Input	XT1
P10 to P17	Input/ output	Port 1 8-bit input/output port. Input/output can be specified bit-wise. When used as an input port, on-chip pull-up resistor can be used in software. Note 2		Input	ANI0 to ANI7
P20	Input/	Port 2		Input	SI1
P21	output	8-bit input/outpu			SO1
P22			n be specified bit-wise. an input port, on-chip pull-up resistor can be used		SCK1
P23		in software.	Tiliput port, oil-cliip puil-up resistor carribe useu		STB
P24					BUSY
P25					SI0/SB0
P26					SO0/SB1
P27					SCK0
P30	Input/	Port 3		Input	TO0
P31	output	8-bit input/outpu			TO1
P32			n be specified in 1-bit units. an input port, on-chip pull-up resistor can be used		TO2
P33		in software.			TI1
P34					TI2
P35					PCL
P36					BUZ
P37					_
P40 to P47	Input/ output	When used as a in software.	ut port. n be specified in 8-bit unit. an input port, on-chip pull-up resistor can be used KRIF) is set to 1 by falling edge detection.	Input	AD0 to AD7

- **Notes 1.** When using the P04/XT1 pins as an input port, set 1 to bit 6 (FRC) of the processor clock control register (PCC). Do not use the on-chip feedback register of the subsystem clock oscillator.
 - 2. When using the P10/ANI0 to P17/ANI7 pins as the A/D converter analog input, on-chip pull-up resistor is automatically unused.





3.1 PORT PINS (2/2)

Pin Name	I/O	Ft	unction	On Reset	Dual- Function Pin		
P50 to P57	Input/ output	Port 5 8-bit input/output port. LED can be driven directly. Input/output can be specified bit-wise. When used as an input port, on-chip pull-up resistor can be used in software.		8-bit input/output port. LED can be driven directly. Input/output can be specified bit-wise. When used as an input port, on-chip pull-up resistor can be used in		Input	A8 to A15
P60 P61 P62 P63	Input/ output	Port 6 8-bit input/output port. Input/output can be specified bit-wise.	N-ch open-drain input/output port. On-chip pull-up resistor can be specified by mask option. LED can be driven directly.	Input			
P64 P65 P66			When used as an input port, on-chip pull-up resistor can be used in software.		RD WR WAIT		
P67					ASTB		

3.2 PINS OTHER THAN PORT PINS (1/2)

Pin Name	I/O	Function	On Reset	Dual- Function Pin
INTP0	Input	External interrupt request input by which the effective edge (rising	Input	P00/TI0
INTP1		edge, falling edge, or both rising edge and falling edge) can be		P01
INTP2		specified.		P02
INTP3		Falling edge detection external interrupt request input.		P03
SI0	Input	Serial interface serial data input.	Input	P25/SB0
SI1				P20
SO0	Output	Serial interface serial data output.	Input	P26/SB1
SO1				P21
SB0	Input	Serial interface serial data input/output.	Input	P25/SI0
SB1	/output			P26/SO0
SCK0	Input	Serial interface serial clock input/output.	Input	P27
SCK1	/output			P22
STB	Output	Serial interface automatic transmit/receive strobe output.	Input	P23
BUSY	Input	Serial interface automatic transmit/receive busy input.	Input	P24





3.2 PINS OTHER THAN PORT PINS (2/2)

Pin Name	I/O	Function	On Reset	Dual- Function Pin
TI0	Input	External count clock input to 16-bit timer (TM0).	Input	P00/INTP0
TI1		External count clock input to 8-bit timer (TM1).		P33
TI2		External count clock input to 8-bit timer (TM2).		P34
TO0	Output	16-bit timer (TM0) output (shared as 14-bit PWM output).	Input	P30
TO1		8-bit timer (TM1) output.		P31
TO2		8-bit timer (TM2) output.		P32
PCL	Output	Clock output (for main system clock, subsystem clock trimming).	Input	P35
BUZ	Output	Buzzer output.	Input	P36
AD0 to AD7	Input /output	Low-order address/data bus at external memory expansion.	Input	P40 to P47
A8 to A15	Output	High-order address bus at external memory expansion.	Input	P50 to P57
RD	Output	External memory read operation strobe signal output.		P64
WR		External memory write operation strobe signal output.		P65
WAIT	Input	Wait insertion at external memory access.	Input	P66
ASTB	Output	Strobe output which latches the address information output at port 4 and port 5 to access external memory.	Input	P67
ANI0 to ANI7	Input	A/D converter analog input.	Input	P10 to P17
AVREF	Input	A/D converter reference voltage input.	_	_
AVDD	_	A/D converter analog power supply. Connected to V _{DD} .	_	_
AVss	_	A/D converter ground potential. Connected to Vss.	_	_
RESET	Input	System reset input.	_	_
X1	Input	Main system clock oscillation crystal connection.	_	_
X2	_		_	_
XT1	Input	Subsystem clock oscillation crystal connection.	Input	P04
XT2	_		_	_
VDD		Positive power supply.	_	_
Vss	_	Ground potential.	_	_
IC	_	Internal connection. Connected to Vss directly.	_	_





3.3 PIN I/O CIRCUITS AND RECOMMENDED CONNECTION OF UNUSED PINS

The input/output circuit type of each pin and recommended connection of unused pins are shown in Table 3-1. For the input/output circuit configuration of each type, refer to **Figure 3-1**.

Table 3-1. Input/Output Circuit Type of Each Pin

Pin Name	Input/output Circuit Type	I/O	Recommended Connection when Not Used
P00/INTP0/TI0	2	Input	Connected to Vss.
P01/INTP1	8-A	Input/output	Individually connected to Vss via resistor.
P02/INTP2			
P03/INTP3			
P04/XT1	16	Input	Connected to VDD or Vss.
P10/ANI0 to P17/ANI7	11	Input/output	Individually connected to VDD or Vss via resisitor.
P20/SI1	8-A		
P21/SO1	5-A		
P22/SCK1	8-A		
P23/STB	5-A		
P24/BUSY	8-A		
P25/SI0/SB0	10-A		
P26/SO0/SB1			
P27/SCK0			
P30/TO0	5-A		
P31/TO1			
P32/TO2			
P33/TI1	8-A		
P34/TI2			
P35/PCL	5-A		
P36/BUZ			
P37			
P40/AD0 to P47/AD7	5-E		Individually connected to VDD via resistor.
P50/A8 to P57/A15	5-A		Individually connected to VDD or Vss via resistor.
P60 to P63	13-B		Individually connected to VDD via resistor.
P64/RD	5-A		Individually connected to VDD or Vss via resistor.
P65/WR			
P66/WAIT			
P67/ASTB			
RESET	2	Input	_
XT2	16	_	Leave open.
AVREF			Connected to Vss.
AVDD			Connected to VDD.
AVss			Connected to Vss.
IC			Connected to Vss directly.



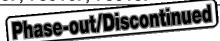
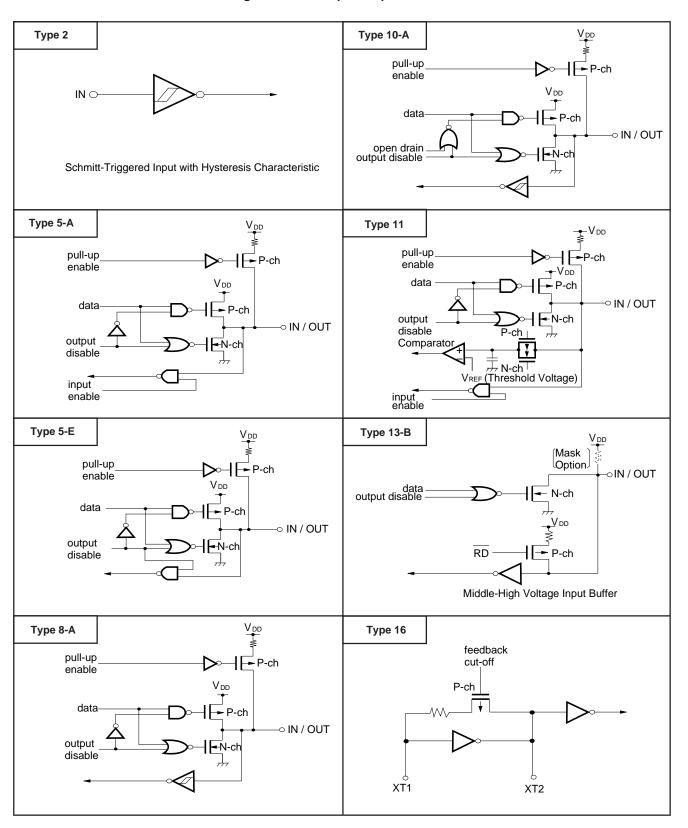


Figure 3-1. Pin Input/Output Circuits





★ 4. MEMORY SPACE

The memory maps of the μ PD78011F, 78012F, 78013F, 78014F, 78015F, 78016F, and 78018F are shown in Figure 4-1 and 4-2.

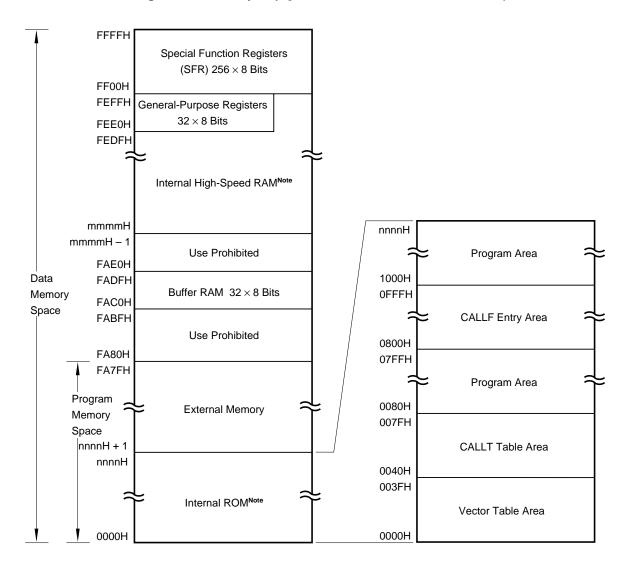


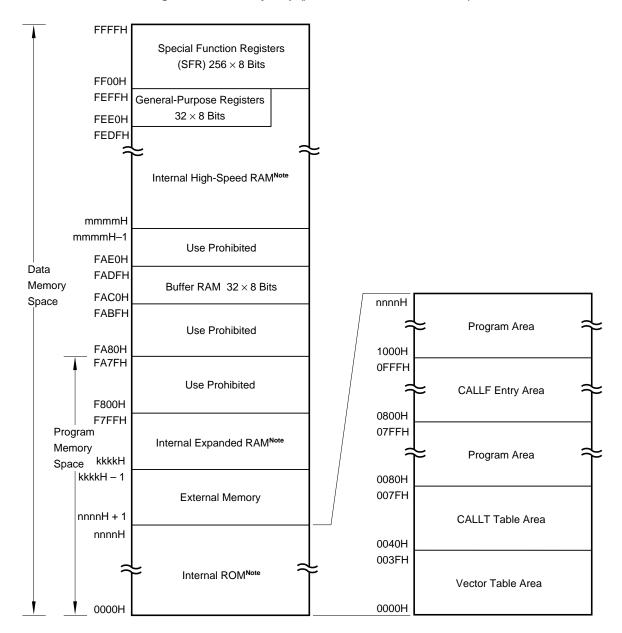
Figure 4-1. Memory Map (μPD78011F, 78012F, 78013F, 78014F)

Note Intermal ROM and internal high-speed RAM capacities vary depending on the product (refer to the table below).

Product Name	Intenal ROM End Address nnnnH	Internal High-Speed RAM Start Address mmmmH
μPD78011F	1FFFH	FD00H
μPD78012F	3FFFH	
μPD78013F	5FFFH	FB00H
μPD78014F	7FFFH	



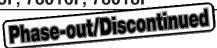
Figure 4-2. Memory Map (µPD78015F, 78016F, 78018F)



Note Intermal ROM, internal high-speed RAM, and internal expanded RAM capacities vary depending on the product (refer to the table below).

Product Name	Intenal ROM End Address nnnnH	Internal High-Speed RAM Start Address mmmmH	Internal Expanded RAM Start Address kkkkH
μPD78015F	9FFFH	FB00H	F600H
μPD78016F	BFFFH		
μPD78018F	EFFFH		F400H





5. PERIPHERAL HARDWARE FUNCTION FEATURES

5.1 PORTS

The I/O port has the following three types

CMOS input (P00, P04)
 CMOS input/output (P01 to P03, port 1 to port 5, P64 to P67)
 N-ch open-drain input/output(15V withstand voltage) (P60 to P63)
 Total

Table 5-1. Functions of Ports

Port Name	Pin Name	Function
Port 0	P00, P04	Dedicated Input port
	P01 to P03	Input/output ports. Input/output can be specified bit-wise.
		When used as an input port, pull-up resistor can be used in software.
Port 1	P10 to P17	Input/output ports. Input/output can be specified bit-wise.
		When used as an input port, pull-up resistor can be used in software.
Port 2	P20 to P27	Input/output ports. Input/output can be specified bit-wise.
		When used as an input port, pull-up resistor can be used in software.
Port 3	P30 to P37	Input/output ports. Input/output can be specified bit-wise.
		When used as an input port, pull-up resistor can be used in software.
Port 4	P40 to P47	Input/output ports. Input/output can be specified in 8-bit units.
		When used as an input port, pull-up resistor can be used in software.
		Test input flag (KRIF) is set to 1 by falling edge detection.
Port 5	P50 to P57	Input/output ports. Input/output can be specified bit-wise.
		When used as an input port, pull-up resistor can be used in software.
		LED can be driven directly.
Port 6	P60 to P63	N-ch open-drain input/output port. Input/output can be specified bit-wise.
		On-chip pull-up resistor can be specified by mask option.
		LED can be driven directly.
	P64 to P67	Input/output ports. Input/output can be specified bit-wise.
		When used as an input port, pull-up resistor can be used in software.

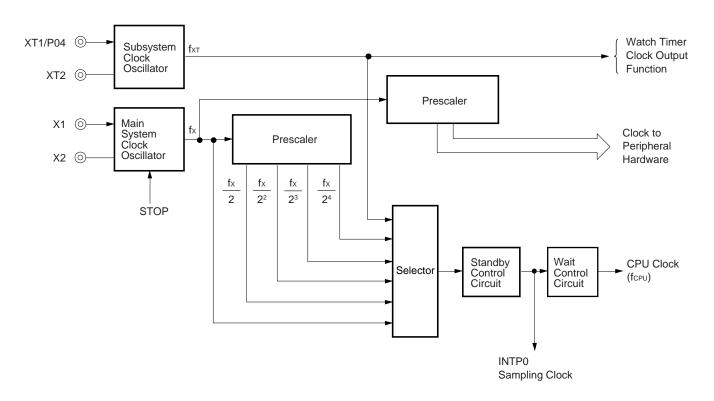


5.2 CLOCK GENERATOR

There are two types of clock generator: main system clock and subsystem clock. The minimum instruction exection time can be changed.

- 0.4μ s/ 0.8μ s/ 1.6μ s/ 3.2μ s/ 6.4μ s (Main system clock: at 10.0 MHz operation)
- 122μs (Subsystem clock: at 32.768 KHz operation)

Figure 5-1. Clock Generator Block Diagram





5.3 TIMER/EVENT COUNTER

The following five channels are incorporated in the timer/event counter.

16-bit timer/event counter
 8-bit timer/event counter
 Watch timer
 Watchdog timer
 1 channel
 1 channel
 1 channel

Table 5-2. Operation of Timer/Event Counter

		16-bit Timer/Event Counter	8-bit Timer/Event Counter	Watch Timer	Watchdog Timer
Operation	Interval timer	1 channel	2 channels	1 channel	1 channel
mode	Externanal event counter	1 channel	2 channels	_	_
Functions	Timer output	1 output	2 outputs	_	_
	PWM output	1 output	_	_	_
	Pulse width mesurement	1 input	_	_	_
	Sqare wave output	1 output	2 outputs	_	_
	Interrupt request	2	2	1	1
	Test input	-	_	1 input	_

Figure 5-2. 16-bit Timer/Enent Counter Block Diagram

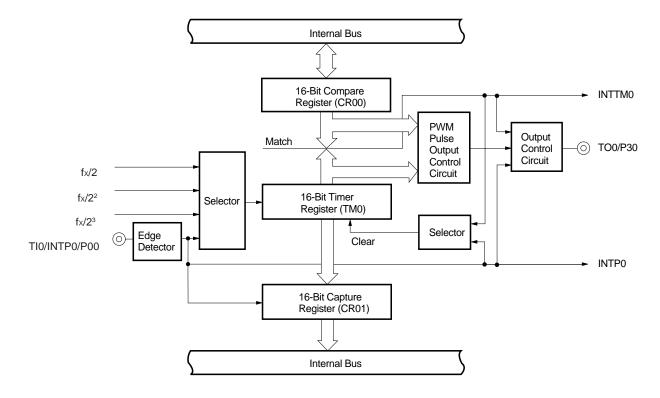




Figure 5-3. 8-bit Timer/Enent Counter Block Diagram

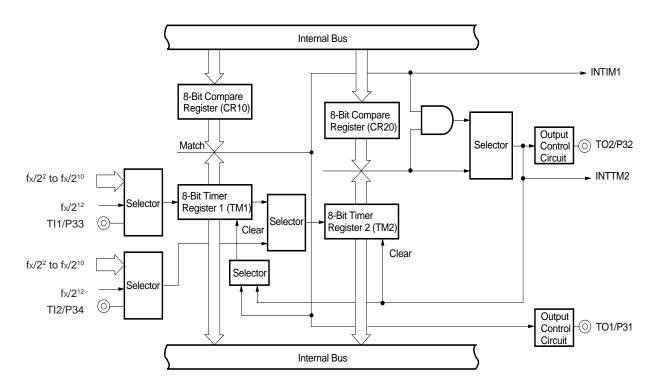


Figure 5-4. Watch Timer Block Diagram

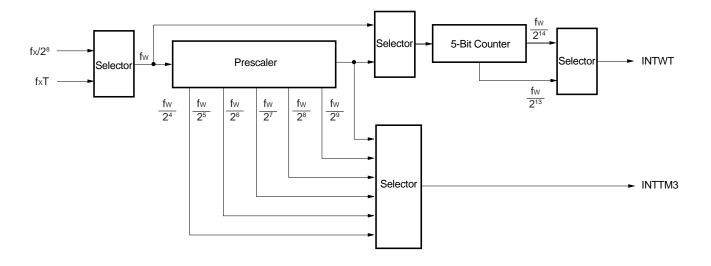
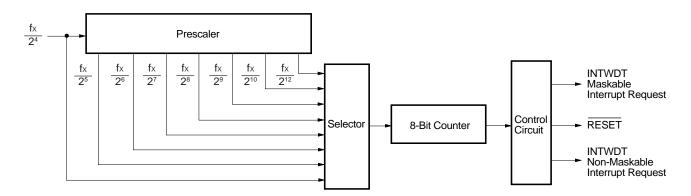




Figure 5-5. Watchdog Timer Block Diagram

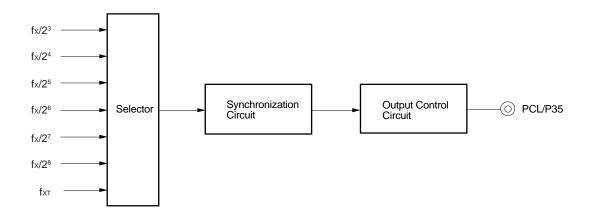


5.4 CLOCK OUTPUT CONTROL CIRCUIT

The clock with the following frequencies can be output for clock output.

- 39.1 kHz/78.1 kHz/156 kHz/313 kHz/625 kHz/1.25 MHz (Main system clock: at 10.0 MHz operation)
- 32.768 kHz (Subsystem clock: at 32.768 kHz operation)

Figure 5-6. Clock Output Control Block Diagram

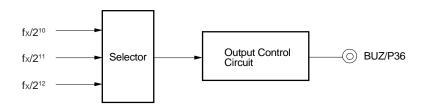


5.5 BUZZER OUTPUT CONTROL CIRCUIT

The clock with the following frequencies can be output for buzzer output.

• 2.4 kHz/4.9 kHz/9.8 kHz (Main system clock: at 10.0 MHz operation)

Figure 5-7. Buzzer Output Control Block Diagram



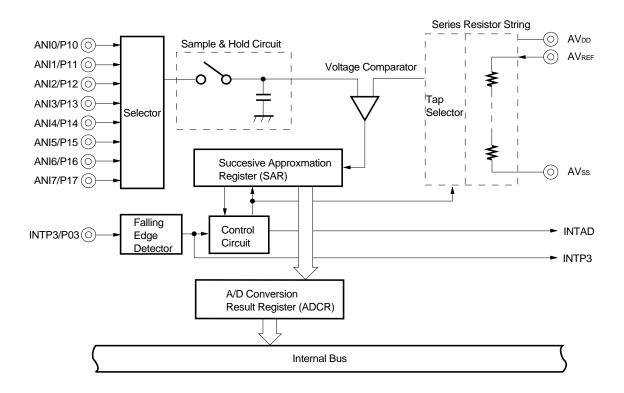


5.6 A/D CONVERTER

The A/D converter has on-chip eight 8-bit resolution channels. There are the following two method to start A/D conversion.

- · Hardware starting
- · Software starting

Figure 5-8. A/D Converter Block Diagram



5.7 SERIAL INTERFACES

There are two on-chip clocked serial interfaces as follows.

- Serial Interface channel 0
- Serial Interface channel 1

Table 5-3. Type and Function of Serial Interface

Function	Serial Interface Channel 0	Serial Interface Channel 1
3-wire serial I/O mode	O (MSB/LSB-first switchable)	O (MSB/LSB-first switchable)
3-wire serial I/O mode with automatic data transmit/ receive function	_	O (MSB/LSB-first switchable)
SBI (Serial Bus Interface) mode	O (MSB-first)	-
2-wire serial I/O mode	O (MSB-first)	-



Figure 5-9. Serial Interface Channel 0 Block Diagram

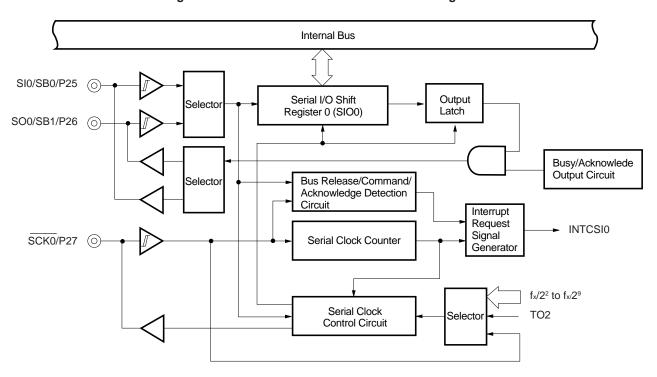
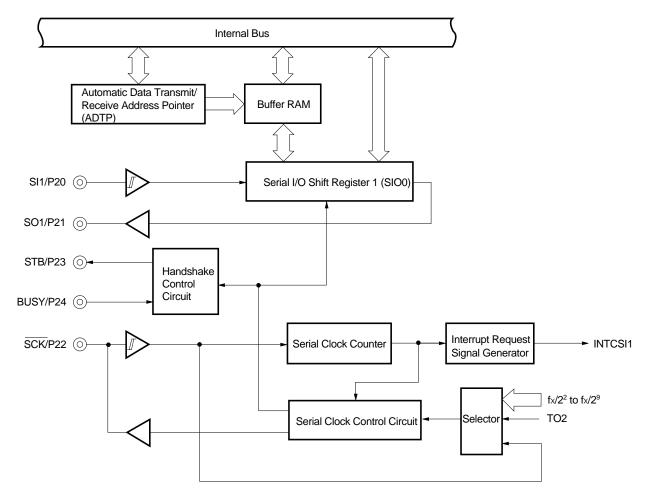
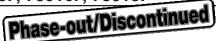


Figure 5-10. Serial Interface Channel 1 Block Diagram







6. INTERRUPT FUNCTIONS AND TEST FUNCTIONS

6.1 INTERRUPT FUNCTIONS

There are interrupt functions, 14 sources of three different kinds, as shown below.

Non-maskable : 1
 Maskable : 12
 Software : 1

Table 6-1. Interrupt Source List

	Default		Interrupt Source	Internal/	Vector Table	Basic
Interrupt Type	Priority Note 1	Name	Trigger	External	Address	Configuratin Type Note 2
Non-maskable		INTWDT	Watchdog timer overflow (with watchdog timer mode 1 selected)	Internal	0004H	(A)
Maskable	0	INTWDT	Watchdog timer overflow (with interval timer mode selected)			(B)
	1	INTP0	Pin input edge detection	External	0006H	(C)
	2	INTP1			0008H	(D)
	3	INTP2			000AH	
	4	INTP3			000CH	
	5	INTCSI0	Serial interface channel 0 transfer end	Internal	000EH	(B)
	6	INTCSI1	Serial interface channel 1 transfer end		0010H	
	7	INTTM3	Reference time interval signal from watch timer		0012H	
	8	INTTM0	16 bit timer/event counter match signal generation		0014H	
	9	INTTM1	8-bit timer/event counter 1 match signal generation		0016H	
	10	INTTM2	8-bit timer/event counter 2 match signal generation		0018H	
	11	INTAD	A/D converter conversion end		001AH	
Software		BRK	BRK instruction execution		003EH	(E)

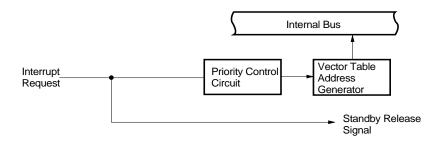
Notes 1. The default pririty is the priority applicable when more than one maskable interrupt request is generated. 0 is the highest priority and 11, the lowest.

2. Basic configuration types (A) to (E) correspond to (A) to (E) on the next page.

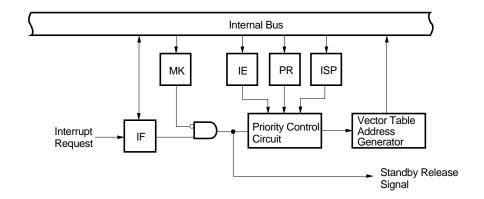


Figure 6-1. Basic Interrupt Function Configuration (1/2)

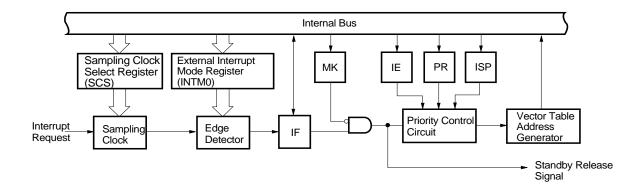
(A) Internal Non-Maskable Interrupt



(B) Internal Maskable Interrupt



(C) External Maskable Interrupt (INTP0)





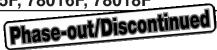
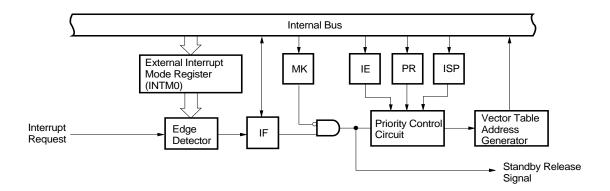
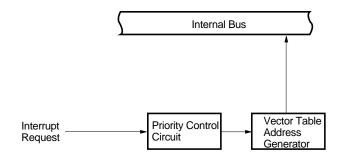


Figure 6-1. Basic Interrupt Function Configuration (2/2)

(D) External Maskable Interrupt (Except INTP0)



(E) Software Interrupt



IF : Interrupt request flag
IE : Interrupt enable flag
ISP : In-service priority flag
MK : Interrupt mask flag
PR : Priority spcification flag



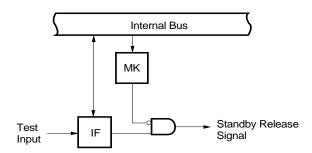
6.2 TEST FUNCTIONS

There are two test functions as shown in Table 6-2.

Table 6-2. Test Source List

	Test Source					
Name Trigger		Internal/External				
INTWT	Watch timer overflow	Internal				
INTPT4	Port 4 falling edge detection	External				

Figure 6-2. Test Function Basic Configuration



IF : Test input flagMK : Test mask flag





7. EXTERNAL DEVICE EXPANSION FUNCTIONS

The external device expansion function is used to connect external devices to areas other than the internal ROM, RAM and SFR.

Ports 4 to 6 are used for connection with external devices.

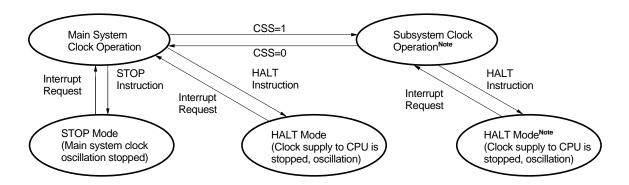
8. STANDBY FUNCTIONS

There are the following two standby functions to reduce the current dissipation.

• HALT mode : The CPU operating clock is stopped. The average consumption current can be reduced by intermittent operation in combination with the normal operating mode.

• STOP mode : The main system clock oscillation is stopped. The whole operation by the main system clock is stopped, so that the system operates withultra-low power consumption using only the subsystem clock.

Figure 8-1. Standby Functions



Note The power consumption can be reduced by stopping the main system clock. When the CPU is operating on the subsystem clock, set the bit 7 (MCC) of the processor clock control register (PCC) to stop the main system clock. The STOP instruction cannot be used.

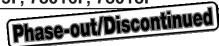
Caution When the main system clock is stopped and the system is operated by the subsystem clock, the subsystem clock should be switched again to the main system clock after the oscillation stabilization time is secured by the program by the program.

9. RESET FUNCTIONS

There are the following two reset methods.

- External reset input by RESET pin.
- Internal reset by watchdog timer runaway time detection.





10. INSTRUCTION SET

(1) 8-Bit Instruction

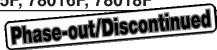
MOV, XCH, ADD, ADDC, SUB, SUBC, AND, OR, XOR, CMP, MULU, DIVUW, INC, DEC, ROR, ROL, RORC, ROLC, ROR4, ROL4, PUSH, POP, DBNZ

Move Move	ROLC, R	OR4, F	KOL4, F	705H, P	OP, DE	SINZ								
A ADD ADDC ADDC ADDC ADDC ADDC ADDC ADD	2nd Operand	#byte	А	r Note	sfr	saddr	!addr16	PSW	[DE]	[HL]	[HL+B]		1	None
ADD ADDC SUB SUBC AND OR XOR CMP Sadder MOV MOV ADD ADDC SUB SUBC AND OR XOR CMP ADDC SUB ADDC SUB AND OR XOR CMP ADDC ADDC ADDC ADDC SUB AND ADDC ADDC	A	ADDC SUB SUBC AND OR XOR		XCH ADD ADDC SUB SUBC AND OR XOR		XCH ADD ADDC SUB SUBC AND OR XOR	XCH ADD ADDC SUB SUBC AND OR XOR	MOV		XCH ADD ADDC SUB SUBC AND OR XOR	MOV XCH ADD ADDC SUB SUBC AND OR XOR		ROL RORC	
sfr MOV MOV MOV MOV MOV MOV MOV DBNZ INC DEC INC INC DEC DEC INC DEC DEC <td>r</td> <td>MOV</td> <td>MOV</td> <td>ADDC SUB SUBC AND OR XOR</td> <td></td> <td></td> <td></td> <td></td> <td></td> <td></td> <td></td> <td></td> <td></td> <td>INC DEC</td>	r	MOV	MOV	ADDC SUB SUBC AND OR XOR										INC DEC
Sadder	B, C											DBNZ		
ADD	sfr	MOV	MOV											
PSW MOV MOV PUSH POP [DE]	sadder	SUBC AND OR XOR	ADD ADDC									DBNZ		INC DEC
[DE] MOV ROR4 [HL] MOV ROR4 [HL+byte] MOV [HL+B] [HL+C] X MULU	!adder16		MOV											
[HL] MOV ROR4 ROL4 [HL+byte] [HL+B] [HL+C] X MULU	PSW	MOV	MOV											PUSH POP
ROL4 ROL4	[DE]		MOV											
[HL+B] [HL+C] X	[HL]		MOV											ROR4 ROL4
	[HL+byte] [HL+B] [HL+C]		MOV											
C DIVUV	Х													MULU
	С													DIVUW

Note Except r=A

*





(2) 16-Bit Instruction

MOVW, XCHW ADDW, SUBW, CMPW, PUSH, POP, INCW, DECW

2nd Operand 1st Operand	#byte	AX	rp ^{Note}	saddrp	!addr16	SP	None	
AX	ADDW		MOVW	MOVW	MOVW	MOVW	MOVW	
	SUBW		XCHW					
	CMPW							
rp	MOVW	MOVWNote						INCW, DECW
								PUSH, POP
sfrp	MOVW	MOVW						
sadderp	MOVW	MOVW						
!adder16		MOVW						
SP	MOVW	MOVW						

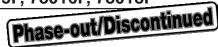
Note Only when rp=BC, DE, HL.

(3) Bit Manipulation Instruction

MOV1, AND1, OR1, XOR1, SET1, CLR1, NOT1, BT, BF, BTCLR

2nd Operand 1st Operand	A.bit	sfr.bit	saddr.bit	PWS.bit	[HL].bit	CY	\$addr16	None
A.bit						MOV1	BT BF BTCLR	SET1 CLR1
sfr.bit						MOV1	BT BF BTCLR	SET1 CLR1
saddr.bit						MOV1	BT BF BTCLR	SET1 CLR1
PSW.bit						MOV1	BT BF BTCLR	SET1 CLR1
[HL].bit						MOV1	BT BF BTCLR	SET1 CLR1
CY	MOV1 AND1 OR1 XOR1	MOV1 AND1 OR1 XOR1	MOV1 AND1 OR1 XOR1	MOV1 AND1 OR1 XOR1	MOV1 AND1 OR1 XOR1			SET1 CLR1 NOT1





(4) Call Instruction/Branch Instruction

CALL, CALLF, CALLT, BR, BC, BNC, BZ, BNZ, BT, BF, BTCLR, DBNZ

2nd Operand 1st Operand	AX	!addr16	!addr11	[addr5]	\$addr16
Basic instruction	BR	CALL, BR	CALLF	CALLT	BR, BC, BNC, BZ, BNZ
Compound instruction					BT,BF,BTCLR, DBNZ

(5) Other Instruction

ADJBA, ADJBS, BRK, RET, RETI, RETB, SEL, NOP, EI, DI, HALT, STOP





11. ELECTRICAL SPECIFICATIONS

Absolute Maximum Ratings ($T_A = 25 \, ^{\circ}C$)

Parameter	Symbol	Test Conditions		Rating	Unit
Supply voltage	Vdd			-0.3 to +7.0	V
	AVDD			−0.3 to V _{DD} + 0.3	V
	AVREF			-0.3 to V _{DD} + 0.3	V
	AVss			-0.3 to +0.3	V
Input voltage	VI1	P00 to P04, P10 to P17, P20 to		-0.3 to V _{DD} + 0.3	V
		P40 toP47, P50 to P57, P64 to	P67, X1, X2, XT2		
	V ₁₂	P60 to P67	Open-drain	-0.3 to +16	V
Output voltage	Vo			-0.3 to $V_{DD} + 0.3$	V
Analog input voltage	Van	P10 to P17	Analog input pin	$AV_{SS} - 0.3$ to $AV_{REF} + 0.3$	V
Output		1 pin		-10	mA
current high	Іон	P10 to P17, P20 to P27, P30 to	P37 total	-15	mA
		P01 to P03, P40 to P47, P50 to P5	7, P60 to P67 total	-15	mA
Output			Peak value	30	mA
current low		1 pin	rms	15	mA
		P40 to P47, P50 to P55 total	Peak value	100	mA
			rms	70	mA
		P01 to P03, P56, P57,	Peak value	100	mA
	_{OL} Note	P60 to P67 total	rms	70	mA
		P01 to P03,	Peak value	50	mA
		P64 to P67 total	rms	20	mA
		P10 to P17, P20 to P27, P30 to P37	Peak value	50	mA
		total	rms	20	mA
Operating ambient temperature	Та			-40 to +85	°C
Storage temperature	Tstg			−65 to +150	°C

Note rms should be calculated as follows: [rms] = [peak value] $\times \sqrt{\text{duty}}$

Caution Product quality may suffer if the absolute maximum rating is exceeded for even a single parameter or even momentarily. That is, the absolute maximuam ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions which ensure that the absolute maximum ratings are not exceeded.





Capacitance (TA = 25 °C, VDD = Vss = 0 V)

Parameter	Symbol	Test Conditions		MIN.	TYP.	MAX.	Unit
Input capacitance	Cin	f = 1 MHz Unmeasured pins returned to 0 V				15	pF
I/O capacitance			P01 to P03, P10 to P17,				
		f = 1 MHz Unmeasured	P20 to P27, P30 toP37,			15	pF
	Сю	pins returned to 0 V	P40 toP47, P50 to P57,				
			P64 to P67				
			P60 to P63			20	pF

Remark The characteristics of a dual-function pin and a port pin are the same unless specified otherwise.

Main System Clock Oscillation Circuit Characteristics ($T_A = -40$ to +85 °C, $V_{DD} = 1.8$ to 5.5 V)

Resonator	Recommended Circuit	Parameter	Test Conditions	MIN.	TYP.	MAX.	Unit
Ceramic	X1 X2 Vss	Oscillator	2.7 V ≤ V _{DD} ≤ 5.5 V	1		10	NAL I—
resonator	R1	frequency (fx) Note 1	1.8 V ≤ V _{DD} < 2.7 V	1		5	MHz
	#C1 #C2	Oscillation stabilization time Note 2	After V _{DD} reaches oscillator voltage range MIN.			4	ms
Crystal	X1 X2 V _{SS}	Oscillator	2.7 V ≤ V _{DD} ≤ 5.5 V	1		10	MHz
resonator		frequency (fx) Note 1	1.8 V ≤ V _{DD} < 2.7 V	1		5	
	-I□I - -C1C2	Oscillation	V _{DD} = 4.5 to 5.5 V			10	
		stabilization time Note 2				30	ms
External clock	X1 X2	X1 input frequency (fx) Note 1		1.0		10.0	MHz
	μPD74HCU04	X1 input high/low level width (txH, txL)		45		500	ns

- Notes 1. Indicates only oscillation circuit characteristics. Refer to AC Characteristics for instruction execution time.
 - 2. Time required to stabilize oscillation after reset or STOP mode release.
- Cautions 1. When using the main system clock oscillator, wiring the area enclosed with the dotted line should be carried out as follows to avoid an adverse effect from wiring capacitance.
 - Wiring should be as short as possible.
 - Wiring should not cross other signal lines.
 - Wiring should not be placed close to a varying high current.
 - The potential of the oscillator capacitor ground should be the same as Vss.
 - Do not ground wiring to a ground pattern in which a high current flows.
 - Do not fetch a signal from the oscillator.
 - 2. When the main system clock is stopped and the system is operated by the subsystem clock, the subsystem clock should be switched again to the main system clock after the oscillation stabilization time is secured by the program.





Subsystem Clock Oscillation Circuit Characteristics ($T_A = -40$ to +85 °C, $V_{DD} = 1.8$ to 5.5 \overline{V})

Resonator	Recommended Circuit	Parameter	Test Conditions	MIN.	TYP.	MAX.	Unit
Crystal resonator		Oscillator frequency (fxt) Note 1		32	32.768	35	kHz
	#C3 #C4	Oscillation	V _{DD} = 4.5 to 5.5 V		1.2	2	s
		stabilization time Note 2				10	
External clock		XT1 input frequency (fxt) Note 1		32		100	kHz
		XT1 input high/low level width (txth, txtl)		5		15	μs

- Notes 1. Indicates only oscillation circuit characteristics. Refer to AC Characteristics for instruction execution time.
 - 2. Time required to stabilize oscillation after VDD reaches oscillator voltage MIN.
- Cautions 1. When using the subsystem clock oscillator, wiring in the area enclosed with the dotted line should be carried out as follows to avoid an adverse effect from wiring capacitance.
 - Wiring should be as short as possible.
 - Wiring should not cross other signal lines.
 - Wiring should not be placed close to a varying high current.
 - The potential of the oscillator capacitor ground should be the same as Vss.
 - Do not ground wiring to a ground pattern in which a high current flows.
 - Do not fetch a signal from the oscillator.
 - 2. The subsystem clock oscillation circuit is a circuit with a low amplification level, more prone to misoperation due to noise than the main system clock.

Particular care is therefore required with the wiring method when the subsystem clock is used.





★ Recommended Oscillation Circuit Constant

Recommended oscillation circuit constant differs depending on the model.

(1) μ PD78011F, 78012F, 78013F, 78014F

(a) Main system clock: ceramic resonator ($T_A = -45 \text{ to } +85 \text{ }^{\circ}\text{C}$)

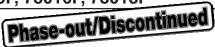
Manufacturer	Product Name	Frequency (MHz)	Recommended Oscillation Circuit Constant		Oscillation Voltage Range		
		(1711 12)	C1 (pF)	C2 (pF)	MIN. (V)	MAX. (V)	
TDK Corp.	CCR4.19MC3	4.19	Built-in	Built-in	1.8	5.5	
	FCR4.19MC5	4.19	Built-in	Built-in	1.8	5.5	
	CCR5.00MC3	5.00	Built-in	Built-in	1.8	5.5	
	FCR5.00MC5	5.00	Built-in	Built-in	1.8	5.5	
	CCR8.38MC	8.00	Built-in	Built-in	2.7	5.5	
	FCR8.38MC5	8.00	Built-in	Built-in	2.7	5.5	
	CCR10.00MC	10.00	Built-in	Built-in	2.7	5.5	
	FCR10.00MC5	10.00	Built-in	Built-in	2.7	5.5	
Murata Mfg. Co. Ltd.	CSA4.19MG	4.19	30	30	1.8	5.5	
	CST4.19MGW	4.19	Built-in	Built-in	1.8	5.5	
	CSA5.00MG	5.00	30	30	1.8	5.5	
	CST5.00MGW	5.00	Built-in	Built-in	1.8	5.5	
	CSA8.38MTZ	8.38	30	30	2.7	5.5	
	CST8.38MTW	8.38	Built-in	Built-in	2.7	5.5	
	CSA10.00MTZ	10.00	30	30	2.7	5.5	
	CST10.00MTW	10.00	Built-in	Built-in	2.7	5.5	

(b) Main system clock: ceramic resonator ($T_A = -20 \text{ to } +80 \text{ }^{\circ}\text{C}$)

Manufacturer	Product Name	Frequency (MHz)	Recommended Oscillation Circuit Constant		Oscillation Voltage Range		
		(1711 12)	C1 (pF)	C2 (pF)	MIN. (V)	MAX. (V)	
Kyocera Corp.	PBRC5.00A	5.00	33	33	1.8	5.5	
	PBRC5.00B	5.00	Built-in	Built-in	1.8	5.5	
	KBR-5.00MSA	5.00	33	33	1.8	5.5	
	KBR-5.00MKS	5.00	Built-in	Built-in	1.8	5.5	
	KBR-8M	8.00	33	33	2.7	5.5	
	KBR-10M	10.00	33	33	2.7	5.5	

Caution The oscillation circuit constants and oscillation voltage range indicate conditions for stable oscillation but do not guarantee the accuracy of the oscillation frequency. If the application circuit requires accuracy of the oscillation frequency, it is necessary to set the oscillation frequency of the resonator in the application circuit. For this, it is necessary to directly contact manufacturer of the resonator being used.





(2) μ PD78015F, 78016F

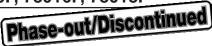
(a) Main system clock: ceramic resonator ($T_A = -45 \text{ to } +85 \text{ }^{\circ}\text{C}$)

Manufacturer	Product Name	Frequency (MHz)		mmended Os Circuit Consta		Oscillation Voltage Range		
		(IVITIZ)	C1 (pF)	C2 (pF)	R1 (kΩ)	MIN. (V)	MAX. (V)	
TDK Corp.	CSB1000J	1.00	100	100	5.6	1.8	6.0	
	CSA2.00MG040	2.00	100	100	0	1.8	6.0	
	CST2.00MG040	2.00	Built-in	Built-in	0	1.8	6.0	
	CSA4.00MG040	4.00	100	100	0	1.8	6.0	
	CST4.00MGW040	4.00	Built-in	Built-in	0	1.8	6.0	
	CSA6.00MG	6.00	30	30	0	1.8	6.0	
	CST6.00MGW	6.00	Built-in	Built-in	0	1.8	6.0	
	CSA10.0MTZ	10.0	30	30	0	1.8	6.0	
	CST10.0MTW	10.0	Built-in	Built-in	0	1.8	6.0	
Murata Mfg. Co. Ltd.	CSA6.00MG040	6.00	100	100	0	2.7	6.0	
(EMI noise reduced	CST6.00MGW040	6.00	Built-in	Built-in	0	2.7	6.0	
products)	CSA10.0MTZ040	10.0	100	100	0	2.7	6.0	
	CST10.0MTW040	10.0	Built-in	Built-in	0	2.7	6.0	
TDK Corp.	FCR4.0MC5	4.0	Built-in	Built-in	2.2	1.8	6.0	
	FCR10.0MC	10.0	Built-in	Built-in	1.0	1.8	6.0	

(b) Main system clock: ceramic resonator ($T_A = -20 \text{ to } +80 \text{ }^{\circ}\text{C}$)

Manufacturer	Product Name	Frequency (MHz)	Recommended Oscillation Circuit Constant		Oscillation Voltage Range	
		(1411 12)	C1 (pF)	C2 (pF)	MIN. (V)	MAX. (V)
Kyocera Corp.	PBRC5.00A	5.00	33	33	1.8	5.5
	PBRC5.00B	5.00	Built-in	Built-in	1.8	5.5
	KBR-5.00MSA	5.00	33	33	1.8	5.5
	KBR-5.00MKS	5.00	Built-in	Built-in	1.8	5.5
	KBR-8M	8.00	33	33	2.7	5.5
	KBR-10M	10.00	33	33	2.7	5.5

Caution The oscillation circuit constants and oscillation voltage range indicate conditions for stable oscillation but do not guarantee the accuracy of the oscillation frequency. If the application circuit requires accuracy of the oscillation frequency, it is necessary to set the oscillation frequency of the resonator in the application circuit. For this, it is necessary to directly contact manufacturer of the resonator being used.



(3) μ PD78018F

(a) Main system clock: ceramic resonator ($T_A = -40 \text{ to } +85 \text{ }^{\circ}\text{C}$)

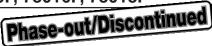
Manufacturer	Product Name	Frequency (MHz)		Recommended Oscillation Circuit Constant		lation Range
		(1011 12)	C1 (pF)	C2 (pF)	MIN. (V)	MAX. (V)
TDK Corp.	CCR4.0MC3	4.00	Built-in	Built-in	1.8	5.5
	FCR4.0MC5	4.00	Built-in	Built-in	1.8	5.5
	CCR8.0MC5	8.00	Built-in	Built-in	2.7	5.5
	FCR8.0MC	8.00	Built-in	Built-in	2.7	5.5
	CCR10.0MC5	10.0	Built-in	Built-in	2.7	5.5
	FCR10.0MC	10.0	Built-in	Built-in	2.7	5.5
Murata Mfg. Co. Ltd.	CSA4.0MG	4.00	30	30	1.8	5.5
	CST4.0MGW	4.00	Built-in	Built-in	1.8	5.5
	CSA8.0MTZ	8.00	30	30	2.7	5.5
	CST8.0MTW	8.00	Built-in	Built-in	2.7	5.5

(b) Main system clock: ceramic resonator ($T_A = -20 \text{ to } +80 \text{ }^{\circ}\text{C}$)

Manufacturer	Product Name	Frequency (MHz)	Recommended Oscillation Circuit Constant		Oscillation Voltage Range		
		(1011 12)	C1 (pF)	C2 (pF)	MIN. (V)	MAX. (V)	
Kyocera Corp.	FBRC4.00A	4.00	33	33	1.8	5.5	
	FBRC4.00B	4.00	Built-in	Built-in	1.8	5.5	
	KBR-4.00MSB	4.00	33	33	1.8	5.5	
	KBR-4.00MKC	4.00	Built-in	Built-in	1.8	5.5	
	KBR-8M	8.00	33	33	2.7	5.5	
	KBR-10M	10.00	33	33	2.7	5.5	

Caution The oscillation circuit constants and oscillation voltage range indicate conditions for stable oscillation but do not guarantee the accuracy of the oscillation frequency. If the application circuit requires accuracy of the oscillation frequency, it is necessary to set the oscillation frequency of the resonator in the application circuit. For this, it is necessary to directly contact manufacturer of the resonator being used.





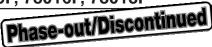
DC Characteristics (TA = -40 to +85 °C, VDD = 1.8 to 5.5 V)

Parameter	Symbol	Test Cond	itions	MIN.	TYP.	MAX.	Unit
Input voltage	V _{IH1}	P10 to P17, P21, P23, P30 to P32,	V _{DD} = 2.7 to 5.5 V	0.7 V _{DD}		V _{DD}	V
high		P35 to P37, P40 to P47,		0.8 Vpd		V _{DD}	V
		P50 to P57, P64 to 67		0.0 VDD		V DD	v
	V _{IH2}	P00 to P03, P20, P22, P24 to P27,	$V_{DD} = 2.7 \text{ to } 5.5 \text{ V}$	0.8 V _{DD}		V _{DD}	V
		P33, P34, RESET		0.85 Vdd		V _{DD}	V
	VIH3	P60 to P63	$V_{DD} = 2.7 \text{ to } 5.5 \text{ V}$	0.7 Vdd		15	V
		(N-ch open-drain)		0.8 VDD		15	V
	V _{IH4}	X1, X2	$V_{DD} = 2.7 \text{ to } 5.5 \text{ V}$	V _{DD} - 0.5		V _{DD}	V
				V _{DD} - 0.2		V _{DD}	V
	V _{IH5}	XT1/P04, XT2	4.5 V ≤ V _{DD} ≤ 5.5 V	0.8 VDD		V _{DD}	V
			2.7 V ≤ V _{DD} < 4.5 V	0.9 V _{DD}		V _{DD}	V
			$1.8 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$ Note	0.9 V _{DD}		V _{DD}	V
Input voltage low	VIL1	P10 to P17, P21, P23, P30 to P32,	V _{DD} = 2.7 to 5.5 V	0		0.3 V _{DD}	V
		P35 to P37, P40 to P47,		0		0.2 Vpp	V
	.,	P50 to P57, P64 to 67		-			
	V _{IL2}	P00 to P03, P20, P22, P24 to P27,	$V_{DD} = 2.7 \text{ to } 5.5 \text{ V}$	0		0.2 V _{DD}	V
		P33, P34, RESET		0		0.15 VDD	V
	V _{IL3} P60 to P63	$4.5 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	0		0.3 V _{DD}	V	
		$2.7 \text{ V} \leq \text{V}_{DD} < 4.5 \text{ V}$	0		0.2 V _{DD}	V	
				0		0.1 V _{DD}	V
	V _{IL4} X1, X2	X1, X2	V _{DD} = 2.7 to 5.5 V	0		0.4	V
				0		0.2	V
	VIL5	XT1/P04, XT2	$4.5~V \leq V_{DD} \leq 5.5~V$	0		0.2 V _{DD}	V
			$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.5 \text{ V}$	0		0.1 V _{DD}	V
			$1.8~V \leq V_{DD} < 2.7~V~^{\mbox{Note}}$	0		0.1 V _{DD}	V
Output	V _{OH1}	$V_{DD} = 4.5 \text{ to } 5.5 \text{ V, IoH} = -1 \text{ mA}$		V _{DD} – 1.0			V
voltage high		I он = $-100 \mu A$		V _{DD} - 0.5			V
Output	V _{OL1}	P50 to P57, P60 to P63	$V_{DD} = 4.5 \text{ to } 5.5 \text{ V},$		0.4	2.0	V
voltage low			loL = 15 mA				
		P01 to P03, P10 to P17, P20 to P27	V _{DD} = 4.5 to 5.5 V,			0.4	V
		P30 to P37, P40 to P47, P64 to P67	IoL = 1.6 mA				
	V _{OL2}	SB0, SB1, SCK0	V _{DD} = 4.5 to 5.5 V, open-drain			0.2 V _{DD}	V
			pulled-up (R = 1 K Ω)				
	V _{OL3}	$I_{OL} = 400 \ \mu A$	/ /			0.5	V

Note When using XT1/P04 as P04, input the inverse of P04 to XT2 using an inverter.

Remark The characteristics of a dual-function pin and a port pin are the same unless specified otherwise.





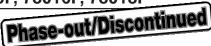
DC Characteristics (TA = -40 to +85 °C, VDD = 1.8 to 5.5 V)

Parameter	Symbol	Test Cond	itions	MIN.	TYP.	MAX.	Unit
Input leakage	ILIH1	VIN = VDD	P00 to P03, P10 to P17,			3	μΑ
current high			P20 to P27, P30 to P37,				
			P40 to P47, P50 to P57,				
			P60 to P67, RESET				
	ILIH2		X1, X2, XT1/P04, XT2			20	μΑ
	Ішнз	Vin = 15 V	P60 to P63			80	μΑ
Input leakege	ILIL1	VIN = 0 V	P00 to P03, P10 to P17,			-3	μΑ
current low			P20 to P27, P30 to P37,				
			P40 to P47, P50 to P57,				
			P60 to P67, RESET				
	ILIL2		X1, X2, XT1/P04, XT2			-20	μΑ
	ILIL3		P60 to P63			_3 Note	μΑ
Output leakage	Ісон1	Vout = VDD				3	μΑ
current high							
Output leakage	ILOL	Vout = 0 V				-3	μΑ
current low							
Mask option	R1	V _{IN} = 0 V, P60 to P63		20	40	90	kΩ
pull-up resister							
Software	R2	V _{IN} = 0 V, P01 to P03, P10 to P17, P20 to P27, P30 to P37,		15	40	90	kΩ
pull-up resister		P40 to P47, P50 to P57, P60 to P67					

Note For P60 to P63, if pull-up resistor is not provided (specifiable by mask option) a low-level input leak current of -200 μ A (MAX.) flows only during the 3 clocks (no-wait time) after an instruction has been executed to read out port 6 (P6) or port mode register 6 (PM6). Outside the period of 3 clocks following execution a read-out instruction, the current is -3 μ A (MAX.).

Remark The characteristics of a dual-function pin and a port pin are the same unless specified otherwise.





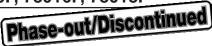
DC Characteristics (TA = -40 to +85 °C, VDD = 1.8 to 5.5 V)

Parameter	Symbol	Test Cond	litions	MIN.	TYP.	MAX.	Unit
Supply	I _{DD1}	10.00 MHz crystal	V _{DD} = 5.0 V ± 10 % Note 2		9.0	18.0	mA
current Note 1		oscillation operation mode	V _{DD} = 3.0 V ± 10 % Note 3		1.3	2.6	mA
	I _{DD2}	10.00 MHz crystal	V _{DD} = 5.0 V ± 10 % Note 2		2.4	4.8	mA
		oscillation HALT mode	V _{DD} = 3.0 V ± 10 % Note 3		1.2	2.4	mA
	IDD3	32.768 kHz crystal	V _{DD} = 5.0 V ± 10 %		60	120	μΑ
		oscillation operation mode Note 4	V _{DD} = 3.0 V ± 10 %		35	70	μΑ
			V _{DD} = 2.0 V ± 10 %		24	48	μΑ
	I _{DD4}	32.768 kHz crystal	V _{DD} = 5.0 V ± 10 %		25	50	μΑ
		oscillation HALT mode Note 4	V _{DD} = 3.0 V ± 10 %		5	15	μΑ
			V _{DD} = 2.0 V ± 10 %		2	10	μΑ
	I _{DD5}	XT1 = V _{DD}	V _{DD} = 5.0 V ± 10 %		1	30	μΑ
		STOP mode when using feedback	V _{DD} = 3.0 V ± 10 %		0.5	10	μΑ
		resistor	V _{DD} = 2.0 V ± 10 %		0.3	10	μΑ
	I _{DD6}	XT1 = VDD	V _{DD} = 5.0 V ± 10 %		0.1	30	μΑ
		STOP mode when not using	V _{DD} = 3.0 V ± 10 %		0.05	10	μΑ
		feedback resistor	V _{DD} = 2.0 V ± 10 %		0.05	10	μΑ

Notes 1. This current excludes the AVREF current, port current, and current which flows in the built-in pull-down resistor.

- 2. When operating at high-speed mode (when the processor clock control register (PCC) is set to 00H)
- 3. When operating at low-speed mode (when the PCC is set to 04H)
- 4. When main system clock stopped.





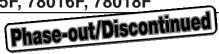
AC Characteristics

(1) Basic Operation (T_A = -40 to +85 °C, V_{DD} = 1.8 to 5.5 V)

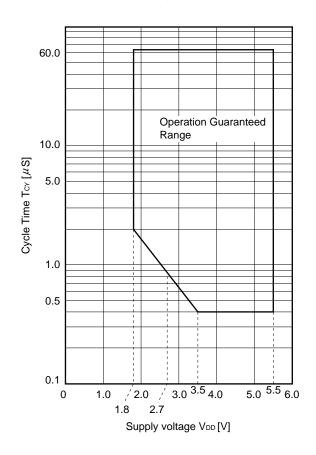
Parameter	Symbol	Test Condition	ons	MIN.	TYP.	MAX.	Unit
Cycle time	Тсч	Operating on main system clock	3.5 V ≤ V _{DD} ≤ 5.5 V	0.4		64	μs
(Min. instruction			2.7 V ≤ V _{DD} < 3.5 V	0.8		64	μs
execution time)			1.8 V ≤ V _{DD} < 2.7 V	2.0		64	μs
		Operating on subsystem clock		40	122	125	μs
TI0 input	t тіно	3.5 V ≤ V _{DD} ≤ 5.5 V		2/f _{sam} + 0.1 Note			μs
frequency	t _{TILO}	2.7 V ≤ V _{DD} < 3.5 V		2/f _{sam} + 0.2 Note			μs
		1.8 V ≤ V _{DD} < 2.7 V		2/f _{sam} + 0.5 Note			μs
TI1, TI2 input	f _{TI1}	V _{DD} = 4.5 to 5.5 V	V _{DD} = 4.5 to 5.5 V			4	MHz
frequency				0		275	kHz
TI1, TI2 input	tтін1	V _{DD} = 4.5 to 5.5 V		100			ns
high/low-level width	tTIL1			1.8			μs
Interrupt	tinth	INTP0	3.5 V ≤ V _{DD} ≤ 5.5 V	2/f _{sam} + 0.1 Note			μs
request input	tintl		2.7 V ≤ V _{DD} < 3.5 V	2/f _{sam} + 0.2 Note			μs
high/low-level			1.8 V ≤ V _{DD} < 2.7 V	2/f _{sam} + 0.5 Note			μs
width		INTP1 to INTP3, KR0 to KR7	V _{DD} = 2.7 to 5.5 V	10			μs
				20			μs
RESET low	trsl	V _{DD} = 2.7 to 5.5 V		10			μs
level width				20			μs

Note In combination with bits 0 (SCS0) and 1 (SCS1) of sampling clock select register (SCS), selection of fsam is possible between $fX/2^{N+1}$, fX/64 and fx/128 (when N=0 to 4).





Tcy vs VDD (At main system clock operation)







(2) Read/Write Operation (TA = -40 to +85 °C, VDD = 2.7 to 5.5 V)

Parameter	Symbol	Test Conditions	MIN.	MAX.	Unit
ASTB high-level width	tasth		0.5tcy		ns
Address setup time	tads		0.5tcy - 30		ns
Address hold time	tadh		50		ns
Data input time from address	t _{ADD1}			(2.5 + 2n) tey - 50	ns
	tADD2			(3 + 2n) tcy - 100	ns
Data input time from $\overline{RD} \downarrow$	tRDD1			(1 + 2n) tcy - 25	ns
	trdd2			(2.5 + 2n) tcy - 100	ns
Read data hold time	trdh		0		ns
RD low-level width	trdL1		(1.5 + 2n) tcy - 20		ns
	tRDL2		(2.5 + 2n) tcy - 20		ns
$\overline{\text{WAIT}} \downarrow \text{input time from } \overline{\text{RD}} \downarrow$	trdwT1			0.5tcy	ns
	trdwt2			1.5tcY	ns
$\overline{\text{WAIT}} \downarrow \text{input time from } \overline{\text{WR}} \downarrow$	twrwt			0.5tcY	ns
WAIT low-level width	twTL		(0.5 + 2n) tcy + 10	(2 + 2n) tcy	ns
Write data setup time	twps		100		ns
Write data hold time	twoH	Load resistor $\geq 5 \text{ k}\Omega$	20		ns
WR low-level width	twrL1		(2.5 + 2n) tcy - 20		ns
$\overline{RD} \!\!\downarrow delay$ time from $ASTB \!\!\downarrow$	tastrd		0.5tcy - 30		ns
$\overline{\mathrm{WR}} \!\!\downarrow \mathrm{delay}$ time from ASTB $\!\!\downarrow$	tastwr		1.5tcy - 30		ns
ASTB↑ delay time from RD↑ in external fetch	trdast		tcy - 10	tcy + 40	ns
Address hold time from RD↑ in external fetch	trdadh		tcy	tcy + 50	ns
Write data output time from RD↑	trowd	V _{DD} = 4.5 to 5.5 V	0.5tcy + 5	0.5tcy + 30	ns
			0.5tcy + 15	0.5tcy + 90	ns
Write data output time from WR↓	twrwd	V _{DD} = 4.5 to 5.5 V	5	30	ns
			15	90	ns
Address hold time from WR↑	twradh	V _{DD} = 4.5 to 5.5 V	tcy	tcy + 60	ns
			tcy	tcy + 100	ns
RD↑ delay time from WAIT↑	twrd		0.5tcy	2.5tcy + 80	ns
WR↑ delay time from WAIT↑	twrwr		0.5tcy	2.5tcy + 80	ns

Remarks 1. tcy = Tcy/4

2. n indicates number of waits.





(3) Serial Interface ($T_A = -40 \text{ to } +85 \text{ }^{\circ}\text{C}$, $V_{DD} = 1.8 \text{ to } 5.5 \text{ V}$)

(a) Serial Interface Channel 0

(i) 3-wire serial I/O mode (SCK0... Internal clock output)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
SCK0 cycle time	tkcy1	4.5 V ≤ V _{DD} ≤ 5.5 V	800			ns
		2.7 V ≤ V _{DD} < 4.5 V	1600			ns
		2.0 V ≤ V _{DD} < 2.7 V	3200			ns
			4800			ns
SCK0 high/low-level	t _{KH1}	V _{DD} = 4.5 to 5.5 V	tkcy1/2 - 50			ns
width	t _{KL1}		tkcy1/2 - 100			ns
SI0 setup time	tsik1	4.5 V ≤ V _{DD} ≤ 5.5 V	100			ns
(to SCK0↑)		2.7 V ≤ V _{DD} < 4.5 V	150			ns
		2.0 V ≤ V _{DD} < 2.7 V	300			ns
			400			ns
SI0 hold time	t _{KSI1}		400			ns
(from SCK0↑)						
SO0 output delay time	t KSO1	C = 100 pF Note			300	ns
from SCK0↓						

Note C is the load capacitance of SCK0 and SO0 output line.

(ii) 3-wire serial I/O mode (SCK0... External clock input)

Parameter	Symbol	Test Co	onditions	MIN.	TYP.	MAX.	Unit
SCK0 cycle time	tkcy2	4.5 V ≤ V _{DD} ≤ 5.5	5 V	800			ns
		2.7 V ≤ V _{DD} < 4.5	5 V	1600			ns
		2.0 V ≤ V _{DD} < 2.7	7 V	3200			ns
				4800			ns
SCK0 high/low-level	t _{KH2}	4.5 V ≤ V _{DD} ≤ 5.5	5 V	400			ns
width	t _{KL2}	2.7 V ≤ V _{DD} < 4.5	5 V	800			ns
		$2.0 \text{ V} \leq \text{V}_{DD} < 2.7$	7 V	1600			ns
				2400			ns
SI0 setup time	tsık2	$V_{DD} = 2.0 \text{ to } 5.5$	V	100			ns
(to SCK0 ↑)				150			ns
SI0 hold time	tksi2			400			ns
(from SCK0↑)							
SO0 output delay time	t KSO2	C = 100 pF Note	V _{DD} = 2.0 to 5.5 V			300	ns
from SCK0↓						500	ns
SCK0 rise, fall time	t _{R2}	When external of	levice			160	ns
	t _{F2}	expansion funct	ion is used				
		When external	When 16-bit timer			700	ns
		device expansion	output function is				
		function is not	used				
		used	When 16-bit timer			1000	ns
			output function is				
			not used				

Note C is the load capacitance of SO0 output line.





(iii) SBI mode (SCK0... Internal clock output)

Parameter	Symbol	Test Co	nditions	MIN.	TYP.	MAX.	Unit
SCK0 cycle time	tксүз	4.5 V ≤ V _{DD} ≤ 5.5	5 V	800			ns
		2.0 V ≤ V _{DD} < 4.5 V		3200			ns
				4800			ns
SCK0 high/low-level	tкнз	$V_{DD} = 4.5 \text{ to } 6.0 ^{\circ}$	V	tксүз/2 – 50			ns
width	tкıз			tксүз/2 – 150			ns
SB0, SB1 setup time	tsıкз	4.5 V ≤ V _{DD} ≤ 5.5	5 V	100			ns
(to SCK0 ↑)		2.0 V ≤ V _{DD} < 4.5	5 V	300			ns
				400			ns
SB0, SB1 hold time	tкsıз			tксүз/2			ns
(from SCK0↑)							
SB0, SB1output delay	tkso3	$R = 1 k\Omega$,	V _{DD} = 4.5 to 5.5 V	0		250	ns
time from $\overline{\text{SCK0}} \downarrow$		C = 100 pF Note		0		1000	ns
SB0, SB1↓ from SCK0↑	tksb			tксүз			ns
$\overline{\text{SCK0}}\downarrow$ from SB0, SB1 \downarrow	tsвк			tксүз			ns
SB0, SB1 high-level	tsвн			tксүз			ns
width							
SB0, SB1 low-level	tsbl			tксүз			ns
width							

Note R and C are the load resistors and load capacitance of the SB0, SB1 and SCK0 output line.



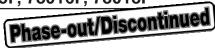


(iv) SBI mode (SCK0... External clock input)

Parameter	Symbol	Test Co	onditions	MIN.	TYP.	MAX.	Unit
SCK0 cycle time	tkcy4	4.5 V ≤ V _{DD} ≤ 5.5	5 V	800			ns
		2.0 V ≤ V _{DD} < 4.5	5 V	3200			ns
				4800			ns
SCK0 high/low-level	t кн4	4.5 V ≤ V _{DD} ≤ 5.5	5 V	400			ns
width	tĸL4	2.0 V ≤ V _{DD} < 4.5	5 V	1600			ns
				2400			ns
SB0, SB1 setup time	tsik4	4.5 V ≤ V _{DD} ≤ 5.5	5 V	100			ns
(to SCK0↑)		2.0 V ≤ V _{DD} < 4.5	5 V	300			ns
				400			ns
SB0, SB1 hold time	tksi4			tkcy4/2			ns
(from SCK0↑)							
SB0, SB1 output delay	tkso4	$R = 1 k\Omega$,	V _{DD} = 4.5 to 5.5 V	0		300	ns
time from SCK0↓		C = 100 pF Note		0		1000	ns
SB0, SB1↓ from SCK0↑	tкsв			tkcy4			ns
SCK0↓ from SB0, SB1↓	tsвк			tkcy4			ns
SB0, SB1 high-level	tsвн			tkcy4			ns
width							
SB0, SB1 low-level	tsbl			tkcy4			ns
width							
SCK0 rise, fall time	t _{R4}	When external d	levice			160	ns
	t _{F4}	expansion functi	on is used				
		When external	When 16-bit timer			700	ns
		device expansion	output function is				
		function is not	used				
		used	When 16-bit timer			1000	ns
			output function is				
			not used				

Note R and C are the load resistors and load capacitance of the SB0 and SB1 output line.





(v) 2-wire serial I/O mode (SCK0... Internal clock output)

Parameter	Symbol	Test Co	nditions	MIN.	TYP.	MAX.	Unit
SCK0 cycle time	tkcy5	$R = 1 k\Omega$,	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	1600			ns
		C = 100 pF Note	$2.0 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$	3200			ns
				4800			ns
SCK0 high-level width	tkH5		$V_{DD} = 2.7 \text{ to } 5.5 \text{ V}$	tkcy5/2 - 160			ns
				tkcy5/2 - 190			ns
SCK0 low-level width	t _{KL5}		$V_{DD} = 4.5 \text{ to } 5.5 \text{ V}$	tkcy5/2 - 50			ns
				tkcy5/2 - 100			ns
SB0, SB1 setup time	tsik5		$4.5 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	300			ns
(to SCK0↑)			$2.7 \text{ V} \le \text{V}_{DD} < 4.5 \text{ V}$	350			ns
			$2.0 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$	400			ns
				500			ns
SB0, SB1 hold time	tksi5			600			ns
(from SCK0↑)							
SB0, SB1 output delay	tksos			0		300	ns
time from SCK0↓							

Note R and C are the load resistors and load capacitance of the $\overline{SCK0}$, SB0 and SB1 output line.





(vi) 2-wire serial I/O mode (SCK0... External clock input)

Parameter	Symbol	Test Co	onditions	MIN.	TYP.	MAX.	Unit
SCK0 cycle time	tkcy6	2.7 V ≤ V _{DD} ≤ 5.5	5 V	1600			ns
		2.0 V ≤ V _{DD} < 2.7	7 V	3200			ns
				4800			ns
SCK0 high-level width	tкн6	2.7 V ≤ V _{DD} ≤ 5.5	5 V	650			ns
		2.0 V ≤ V _{DD} < 2.7	7 V	1300			ns
				2100			ns
SCK0 low-level width	t _{KL6}	2.7 V ≤ V _{DD} ≤ 5.5	5 V	800			ns
		2.0 V ≤ V _{DD} < 2.7	7 V	1600			ns
				2400			ns
SB0, SB1 setup time	tsik6	$V_{DD} = 2.0 \text{ to } 5.5$	V	100			ns
(to SCK0↑)				150			ns
SB0, SB1 hold time	tksi6			tkcy6/2			ns
(from SCK0↑)							
SB0, SB1 output delay	tkso6	$R = 1 k\Omega$,	4.5 V ≤ V _{DD} ≤ 5.5 V	0		300	ns
time from SCK0↓		C = 100 pF Note	2.0 V ≤ V _{DD} < 4.5 V	0		500	ns
				0		800	ns
SCK0 rise, fall time	t _{R6}	When external d	levice			160	ns
	t _{F6}	expansion functi	on is used				
		When external	When 16-bit timer			700	ns
		device expansion	output function is				
		function is not	used				
		used	When 16-bit timer			1000	ns
			output function is				
			not used				

Note R and C are the load resistors and load capacitance of the SB0 and SB1 output line.





(b) Serial Interface Channel 1

(i) 3-wire serial I/O mode (SCK1... Internal clock output)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
SCK1 cycle time	tkcy7	4.5 V ≤ V _{DD} ≤ 5.5 V	800			ns
		2.7 V ≤ V _{DD} < 4.5 V	1600			ns
		$2.0 \text{ V} \leq \text{V}_{DD} < 2.7 \text{ V}$	3200			ns
			4800			ns
SCK1 high/low-level	tкн7	V _{DD} = 4.5 to 5.5 V	tkcy7/2 - 50			ns
width	t _{KL7}		tксүт/2 – 100			ns
SI1 setup time	tsık7	4.5 V ≤ V _{DD} ≤ 5.5 V	100			ns
(to SCK1 ↑)		$2.7 \text{ V} \le \text{V}_{DD} < 4.5 \text{ V}$	150			ns
		$2.0 \text{ V} \leq \text{V}_{DD} < 2.7 \text{ V}$	300			ns
			400			ns
SI1 hold time	t _{KSI7}		400			ns
(from SCK1↑)						
SO1 output delay time	tkso7	C = 100 pF Note			300	ns
from SCK1↓						

Note C is the load capacitance of SCK1 and SO1 output line.

(ii) 3-wire serial I/O mode (SCK1... External clock input)

Parameter	Symbol	Test Co	onditions	MIN.	TYP.	MAX.	Unit
SCK1 cycle time	t ксү8	4.5 V ≤ V _{DD} ≤ 5.5	5 V	800			ns
		2.7 V ≤ V _{DD} < 4.5	5 V	1600			ns
		2.0 V ≤ V _{DD} < 2.7	7 V	3200			ns
				4800			ns
SCK1 high/low-level	tкн8	4.5 V ≤ V _{DD} ≤ 5.5	5 V	400			ns
width	t _{KL8}	2.7 V ≤ V _{DD} < 4.5	5 V	800			ns
		2.0 V ≤ V _{DD} < 2.7	7 V	1600			ns
				2400			ns
SI1 setup time	tsik8	V _{DD} = 2.0 to 5.5	V	100			ns
(to SCK1↑)				150			ns
SI1 hold time	t _{KSI8}			400			ns
(from $\overline{SCK1}\uparrow$)							
SO0 output delay time	tks08	C = 100 pF Note	V _{DD} = 2.0 to 5.5 V			300	ns
from $\overline{\text{SCK1}} \downarrow$						500	ns
SCK1 rise, fall time	t _{R8}	When external of	levice			160	ns
	t _{F8}	expansion functi	on is used				
		When external	When 16-bit timer			700	ns
		device expansion	output function is				
		function is not	used				
		used	When 16-bit timer			1000	ns
			output function is				
			not used				

Note C is the load capacitance of SO1 output line.



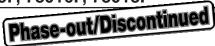


(iii) 3-wire serial I/O mode with automatic transmit/receive function (SCK1... Internal clock output)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
SCK1 cycle time	tkcy9	4.5 V ≤ V _{DD} ≤ 5.5 V	800			ns
		2.7 V ≤ V _{DD} < 4.5 V	1600			ns
		2.0 V ≤ V _{DD} < 2.7 V	3200			ns
			4800			ns
SCK1 high/low-level	t _{KH9}	V _{DD} = 4.5 to 5.5 V	tксү9/2 – 50			ns
width	t _{KL9}		tксү9/2 — 100			ns
SI1 setup time	tsik9	4.5 V ≤ V _{DD} ≤ 5.5 V	100			ns
(to SCK1↑)		$2.7 \text{ V} \leq \text{V}_{DD} < 4.5 \text{ V}$	150			ns
		2.0 V ≤ V _{DD} < 2.7 V	300			ns
			400			ns
SI1 hold time	tksi9		400			ns
(from SCK1↑)						
SO1 output delay time	tks09	C = 100 pF Note			300	ns
from SCK1↓						
STB↑ from SCK1↑	tsbd		tксү9/2 - 100		tксү9/2 + 100	ns
Strobe signal	tsbw	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	tксү9 — 30		tксү9 + 30	ns
high-level width		$2.0 \text{ V} \leq \text{V}_{DD} < 2.7 \text{ V}$	tксү9 — 60		tkcy9 + 60	ns
			tксү9 — 90		tkcy9 + 90	ns
Busy signal setup time	tBYS		100			ns
(to busy signal						
detection timing)						
Busy signal hold time	tвүн	$4.5 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	100			ns
(from busy signal		$2.7~\textrm{V} \leq \textrm{V}_\textrm{DD} < 4.5~\textrm{V}$	150			ns
detection timing)		$2.0 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$	200			ns
			300			ns
SCK1↓ from busy	tsps				2tксү9	ns
inactive						

Note C is the load capacitance of $\overline{\text{SCK1}}$ and SO1 output line.



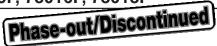


(iv) 3-wire serial I/O mode with automatic transmit/receive function (SCK1... External clock input)

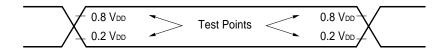
Parameter	Symbol	Test Co	nditions	MIN.	TYP.	MAX.	Unit
SCK1 cycle time	tkcY10	4.5 V ≤ V _{DD} ≤ 5.5	5 V	800			ns
		2.7 V ≤ V _{DD} < 4.5	5 V	1600			ns
		2.0 V ≤ V _{DD} < 2.7	7 V	3200			ns
				4800			ns
SCK1 high/low-level	t кн10,	4.5 V ≤ V _{DD} ≤ 5.5	5 V	400			ns
width	t _{KL10}	2.7 V ≤ V _{DD} < 4.5	5 V	800			ns
		2.0 V ≤ V _{DD} < 2.7	7 V	1600			ns
				2400			ns
SI1 setup time	tsik10	V _{DD} = 2.0 to 5.5	V	100			ns
(to SCK1 ↑)				150			ns
SI1 hold time	tksi10			400			ns
(from SCK1↑)							
SO1 output delay time	t KSO10	C = 100 pF Note	$V_{DD} = 2.0 \text{ to } 5.5 \text{ V}$			300	ns
from SCK1↓						500	ns
SCK1 rise, fall time	tr10, tr10	When external device expansion				160	ns
		function is used					
		When external d	evice expansion			1000	ns
		function is not us	sed				

Note C is the load capacitance of the SO1 output line.

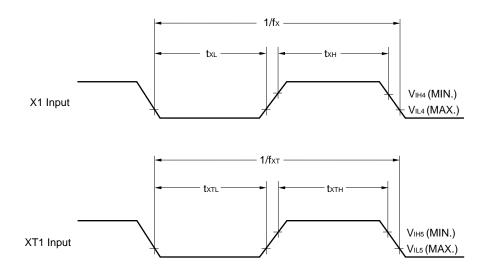




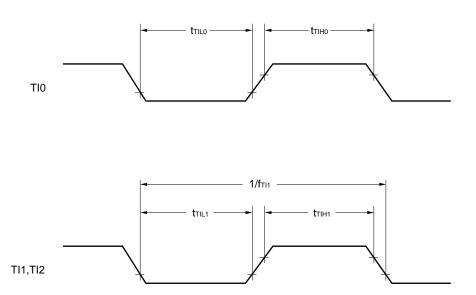
AC Timing Test Point (Excluding X1, XT1 Input)

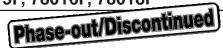


Clock Timing



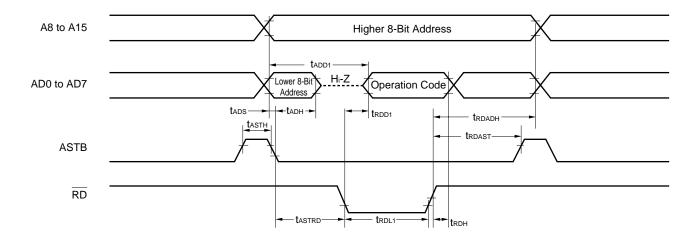
TI Timing



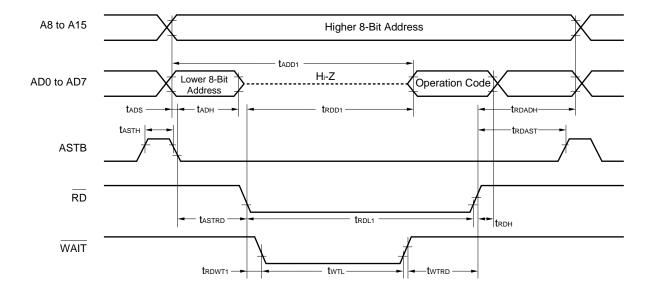


Read/Write Operation

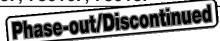
External fetch (No wait):



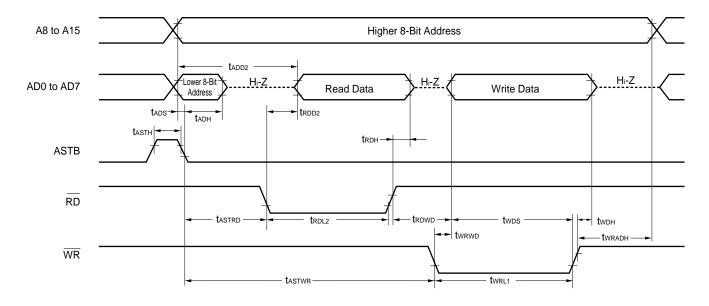
External fetch (Wait insertion):



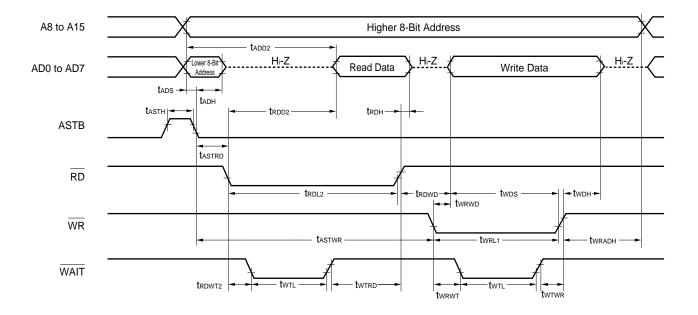




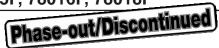
External data access (No wait):



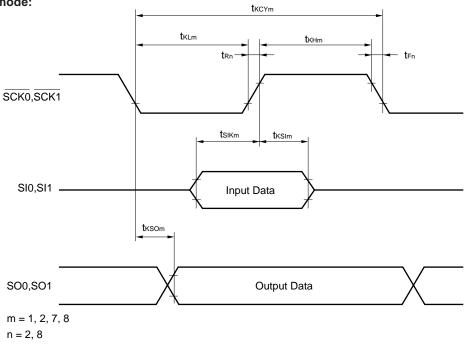
External data access (Wait insertion):



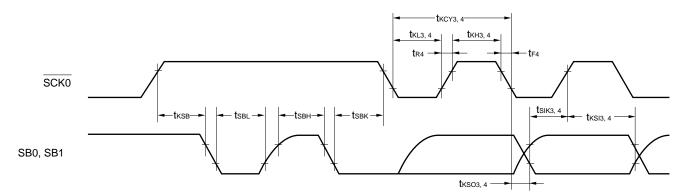




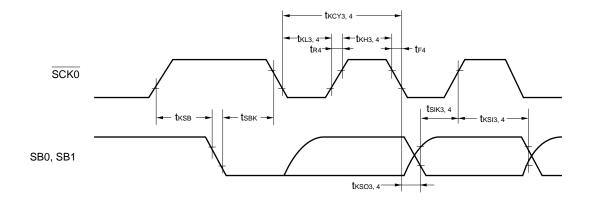
Serial Transfer Timing 3-wire serial I/O mode:



SBI mode (Bus release signal transfer):



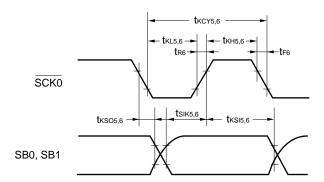
SBI Mode (command signal transfer):



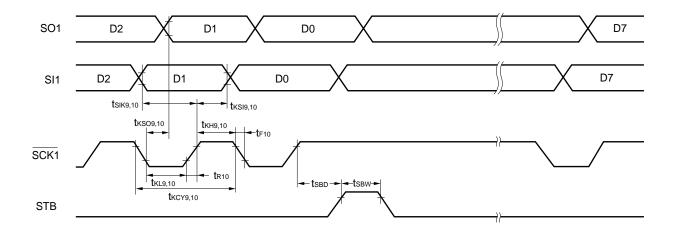


Phase-out/Discontinued

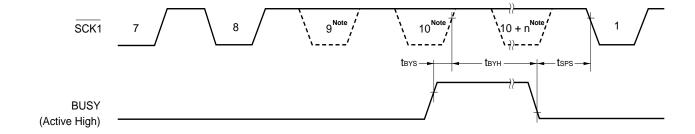
2-wire serial I/O mode:



3-wire serial I/O mode with automatic transmit/receive function:

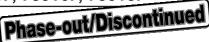


3-wire serial I/O mode with automatic transmit/receive function (busy processing):



Note The signal is not actually driven low here; it is shown as such to indicate the timing.





A/D converter characteristics ($T_A = -40 \text{ to } +85 \text{ }^{\circ}\text{C}$, $AV_{DD} = V_{DD} = 1.8 \text{ to } 5.5 \text{ V}$, $AV_{SS} = V_{SS} = 0 \text{ V}$)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Resolution			8	8	8	bit
Overall error Note		2.7 V ≤ AV _{REF} ≤ AV _{DD}			0.6	%
		1.8 V ≤ AV _{REF} < 2.7 V			1.4	%
Conversion time	tconv	2.0 V ≤ AV _{DD} ≤ 5.5 V	19.1		200	μs
		1.8 V ≤ AV _{DD} < 2.0 V	38.2		200	μs
Sampling time	tsamp		24/fx			μs
Analog input voltage	VIAN		AVss		AVREF	V
Reference voltage	AVREF		1.8		AV _{DD}	V
AV _{REF} resistance	RAIREF		4	14		kΩ

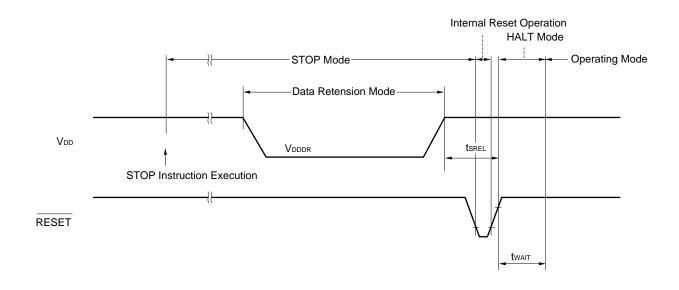
Note Overall error excluding quantization error (±1/2 LSB). It is indicated as a ratio to the full-scale value.

Data Memory STOP Mode Low Supply Voltage Data Retention Characteristics (TA = -40 to +85 °C)

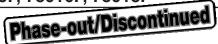
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply	VDDDR		1.8		5.5	V
voltage						
Data retention supply	IDDDR	V _{DDDR} = 1.8 V		0.1	10	μΑ
current		Subsystem clock stop and feed-				
		back resister disconnected				
Release signal set time	tsrel		0			μs
Oscillation stabilization	twait	Release by RESET		2 ¹⁸ /fx		ms
wait time		Release by interrupt request		Note		ms

Note In combination with bit 0 to bit 2 (OSTS0 to OSTS2) of oscillation stabilization time select register (OSTS), selection of 2¹³/fx and 2¹⁵/fx to 2¹⁸/fx is possible.

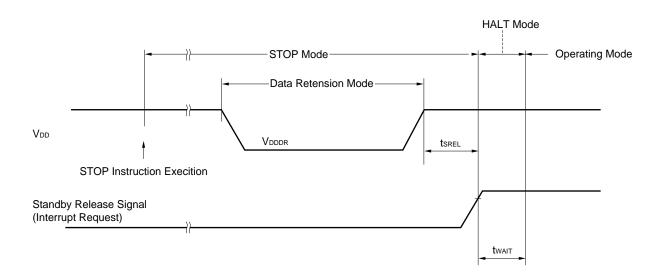
Data Retention Timing (STOP Mode Release by RESET)





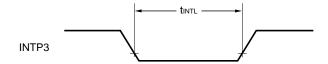


Data Retention Timing (Standby Release Signal: STOP Mode Release by Interrupt Request Signal)

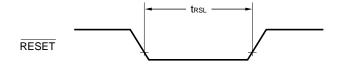


Interrupt Request Input Timing

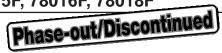




RESET Input Timing

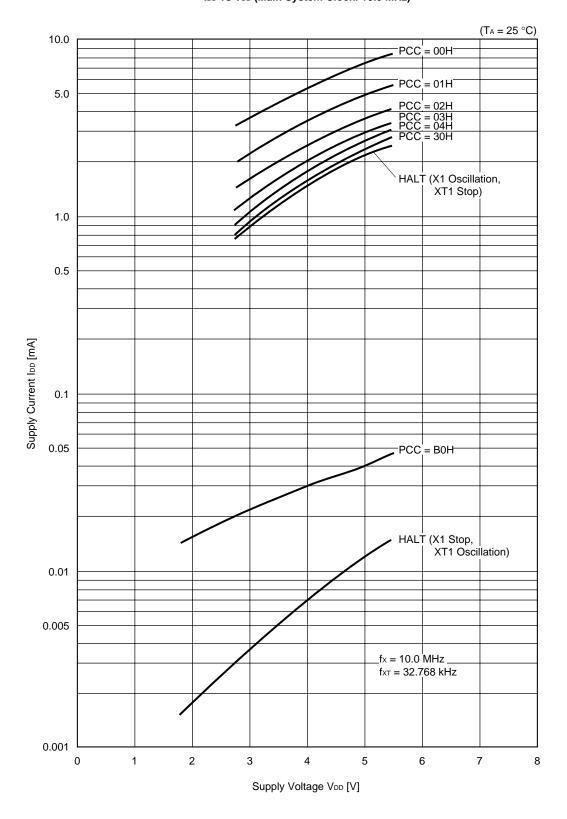






12. CHARACTERISTIC CURVE (REFERENCE VALUES)

IDD vs VDD (Main System Clock: 10.0 MHz)

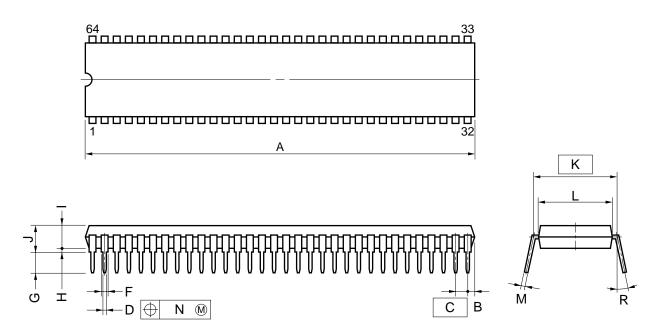






13. PACKAGE DRAWINGS

64 PIN PLASTIC SHRINK DIP (750 mil)



NOTE

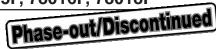
- 1) Each lead centerline is located within 0.17 mm (0.007 inch) of its true position (T.P.) at maximum material condition.
- 2) Item "K" to center of leads when formed parallel.

ITEM	MILLIMETERS	INCHES
Α	58.68 MAX.	2.311 MAX.
В	1.78 MAX.	0.070 MAX.
С	1.778 (T.P.)	0.070 (T.P.)
D	0.50±0.10	$0.020^{+0.004}_{-0.005}$
F	0.9 MIN.	0.035 MIN.
G	3.2±0.3	0.126±0.012
Н	0.51 MIN.	0.020 MIN.
I	4.31 MAX.	0.170 MAX.
J	5.08 MAX.	0.200 MAX.
K	19.05 (T.P.)	0.750 (T.P.)
L	17.0	0.669
М	0.25 ^{+0.10} -0.05	$0.010^{+0.004}_{-0.003}$
Ν	0.17	0.007
R	0~15°	0~15°
	_	

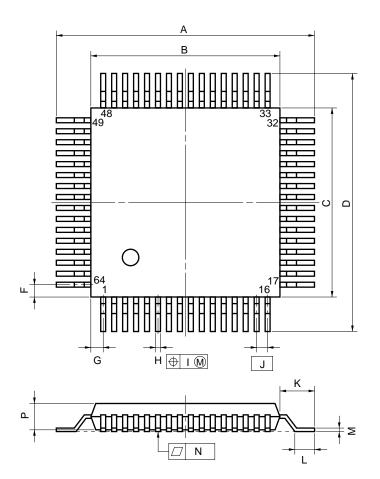
P64C-70-750A,C-1

Remark Dimensions and materials of ES products are the same as those of mass-production products.

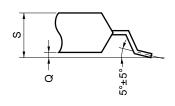




64 PIN PLASTIC QFP (□14)



detail of lead end



NOTE

Each lead centerline is located within 0.15 mm (0.006 inch) of its true position (T.P.) at maximum material condition.

P64GC-80-AB8-2

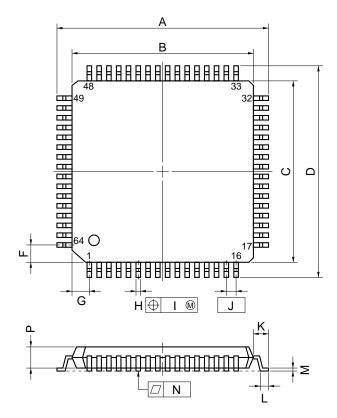
ITEM	MILLIMETERS	INCHES
Α	17.6±0.4	0.693±0.016
В	14.0±0.2	$0.551^{+0.009}_{-0.008}$
С	14.0±0.2	$0.551^{+0.009}_{-0.008}$
D	17.6±0.4	0.693±0.016
F	1.0	0.039
G	1.0	0.039
Н	0.35±0.10	$0.014^{+0.004}_{-0.005}$
I	0.15	0.006
J	0.8 (T.P.)	0.031 (T.P.)
K	1.8±0.2	0.071±0.008
L	0.8±0.2	$0.031^{+0.009}_{-0.008}$
М	$0.15^{+0.10}_{-0.05}$	$0.006^{+0.004}_{-0.003}$
N	0.10	0.004
Р	2.55	0.100
Q	0.1±0.1	0.004±0.004
S	2.85 MAX.	0.112 MAX.

Remark Dimensions and materials of ES products are the same as those of mass-production products.

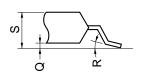




64 PIN PLASTIC LQFP (□12)



detail of lead end



NOTE

Each lead centerline is located within 0.13 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
Α	14.8±0.4	0.583±0.016
В	12.0±0.2	$0.472^{+0.009}_{-0.008}$
С	12.0±0.2	$0.472^{+0.009}_{-0.008}$
D	14.8±0.4	0.583±0.016
F	1.125	0.044
G	1.125	0.044
Н	0.30±0.10	$0.012^{+0.004}_{-0.005}$
ı	0.13	0.005
J	0.65 (T.P.)	0.026 (T.P.)
K	1.4±0.2	0.055±0.008
L	0.6±0.2	$0.024^{+0.008}_{-0.009}$
М	0.15 ^{+0.10} -0.05	$0.006^{+0.004}_{-0.003}$
N	0.10	0.004
Р	1.4	0.055
Q	0.125±0.075	0.005±0.003
R	5°±5°	5°±5°
S	1.7 MAX.	0.067 MAX.

P64GK-65-8A8-1

Remark Dimensions and materials of ES products are the same as those of mass-production products.





14. RECOMMENDED SOLDERING CONDITIONS

The μ PD78011F/78012F/78013F/78014F/78015F/78016F/78018F should be soldered and mounted under the conditions recommended in the table below.

For detail of recommended soldering conditions, refer to the information document **Semiconductor Device Mounting Technology Manual (C10535E)**.

For soldering methods and conditions other than those recommended below, contact our salespersonnel.

Table 14-1. Surface Mounting Type Soldering Conditions (1/2)

```
(1) \muPD78011FGC-\times\times-AB8: 64-Pin Plastic QFP (14 \times 14 mm) \muPD78012FGC-\times\times-AB8: 64-Pin Plastic QFP (14 \times 14 mm) \muPD78013FGC-\times\times-AB8: 64-Pin Plastic QFP (14 \times 14 mm) \muPD78014FGC-\times\times-AB8: 64-Pin Plastic QFP (14 \times 14 mm) \muPD78015FGC-\times\times-AB8: 64-Pin Plastic QFP (14 \times 14 mm) \muPD78016FGC-\times\times-AB8: 64-Pin Plastic QFP (14 \times 14 mm) \muPD78018FGC-\times\times-AB8: 64-Pin Plastic QFP (14 \times 14 mm)
```

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow	Package peak temperature: 235 °C, Duration: 30 sec. max. (at 210 °C or above), Number of times: Three times max.	IR35-00-3
VPS	Package peak temperature: 215 °C, Duration: 40 sec. max. (at 200 °C or above), Number of times: Three times max.	VP15-00-3
Wave soldering	Solder bath temperature: 260 °C max. Duration: 10 sec. max. Number of times: Once Preheating temperature: 120 °C max. (Package surface temperature)	WS60-00-1
Partial heating	Pin temperature: 300 °C max., Duration: 3 sec. max. (per device side)	_

Caution Use more than one soldering method should be avoided (except in the case of partial heating).



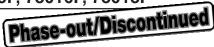


Table 14-1. Surface Mounting Type Soldering Conditions (2/2)

```
(2) \muPD78011FGK-\times\times-8A8 : 64-Pin Plastic LQFP (12 \times 12 mm) \muPD78012FGK-\times\times-8A8 : 64-Pin Plastic LQFP (12 \times 12 mm) \muPD78013FGK-\times\times-8A8 : 64-Pin Plastic LQFP (12 \times 12 mm) \muPD78014FGK-\times\times-8A8 : 64-Pin Plastic LQFP (12 \times 12 mm) \muPD78015FGK-\times\times-8A8 : 64-Pin Plastic LQFP (12 \times 12 mm) \muPD78016FGK-\times\times-8A8 : 64-Pin Plastic LQFP (12 \times 12 mm) \muPD78018FGK-\times\times-8A8 : 64-Pin Plastic LQFP (12 \times 12 mm)
```

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow	Package peak temperature: 235 °C, Duration: 30 sec. max. (at 210 °C or above), Number of times: Twice max., Number of days: 7 days Note (after that, 125 °C prebaking for 10 hours is necessary.) < Precautions > (1) Start the second reflow after the device temprature by the first reflow returns to normal. (2) Flux washing by the water after the first reflow should be avoided.	IR35-107-2
VPS	Package peak temperature: 215 °C, Duration: 40 sec. max. (at 200 °C or above), Number of times: Twice max., Number of days: 7 days Note (after that, 125 °C prebaking for 10 hours is necessary.) < Precautions > (1) Start the second reflow after the device temprature by the first reflow returns to normal. (2) Flux washing by the water after the first reflow should be avoided.	VP15-107-2
Wave soldering	Solder bath temperature: 260 °C max. Duration: 10 sec. max. Number of times: Once, Preheating temperature: 120 °C max. (Package surface temperature), Number of days: 7 days Note (after that, 125 °C prebaking for 10 hours is necessary.)	WS60-107-1
Partial heating	Pin temperature: 300 °C max., Duration: 3 sec. max. (per device side)	_

Note The number of days the device can be stored at 25 °C, 65% RH MAX. after the dry pack has been opend.

Caution Use more than one soldering method should be avoided (except in the case of partial heating).



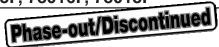


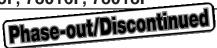
Table 14-2. Insertion Type Soldering Conditions

 μ PD78011FCW- $\times\times\times$: 64-Pin Plastic Shrink DIP (750 mil) μ PD78012FCW- $\times\times\times$: 64-Pin Plastic Shrink DIP (750 mil) μ PD78013FCW- $\times\times\times$: 64-Pin Plastic Shrink DIP (750 mil) μ PD78014FCW- $\times\times\times$: 64-Pin Plastic Shrink DIP (750 mil) μ PD78015FCW- $\times\times\times$: 64-Pin Plastic Shrink DIP (750 mil) μ PD78016FCW- $\times\times\times$: 64-Pin Plastic Shrink DIP (750 mil) μ PD78018FCW- $\times\times\times$: 64-Pin Plastic Shrink DIP (750 mil)

Soldering Method	Soldering Conditions
Wave soldering (pin only)	Solder bath temperature: 260°C max., Duration: 10 sec. max.
Partial heating	Pin temperature: 300°C max., Duration: 3 sec. max. (per pin)

Caution Wave soldering is only for the lead part in order that jet solder can not contact with the chip directly.





APPENDIX A. DEVELOPMENT TOOLS

The following development tools are available for system development using the $\mu PD78018F$ subseries.

Language Processing Software

RA78K/0 Notes 1, 2, 3, 4	78K/0 series common assembler package
CC78K/0 Notes 1, 2, 3, 4	78K/0 series common C compiler package
DF78014 Notes 1, 2, 3, 4	Device file common to μ PD78014 subseries
CC78K/0-L Notes 1, 2, 3, 4	78K/0 series common C compiler library source file

PROM Writting Tools

PG-1500	PROM programmer
PA-78P014CW	Programmer adapter connected to PG-1500
PA-78P018GC	
PA-78P018GK	
PA-78P018KK-S	
PG-1500 controller Notes 1, 2	PG-1500 control program

Debugging Tool

	IE-78000-R	78K/0 series common in-circuit emulator
*	IE-78000-R-A	78K/0 series common in-circuit emulator (for integrated debugger)
	IE-78000-R-BK	78K/0 series common break board
	IE-78014-R-EM-A	μ PD78018F and 78018FY subseries evaluation emulation board (Vpb = 3.0 to 6.0 V)
*	IE-78000-R-SV3	Interface adapter and cable when an EWS is used as the host machine (for IE-78000R-A)
*	IE-70000-98-IF-B	Interface adapter when PC-9800 series (except notebook PC) is used as the host machine (for IE-78000-R-A)
*	IE-70000-98N-IF	Interface adapter and cable when PC-9800 series notebook PC is used as the host machine (for IE-78000-R-A)
*	IE-70000-PC-IF-B	Interface adapter when IBM PC/AT TM is used as the host machine (for IE-78000-R-A)
	EP-78240CW-R EP-78240GC-R	Emulation probe common to μ PD78244 subseries
	EV-78012GK-R	μ PD78018F subseries emulation probe
	EV-9200GC-64	Socket to be mounted on target system board created for the 64-pin plastic QFP (GC-AB8 type)
*	TGC-064SBW	Conversion adapter to be mounted on a target system board made for 64-pin plastic QFP (GK-8A8 type) TGC-100SDW is a product from Tokyo Eletech Corp. (TEL (03) 5295-1661) When purchasing this product, please consult with our sales offices.
	EV-9900	Tools for removing μ PD78P018FKK-S from EV-9200GC-64
	SM78K0 Notes 5, 6, 7	78K/0 series common system simulator
*	ID78K0 Notes 4, 5, 6, 7	IE-78000-R-A integrated dubugger
	SD78K/0 Notes 1, 2	IE-78000-R screen debugger
	DF78014 Notes 1, 2, 4, 5, 6, 7	Device file common to μPD78014 subseries

Real-Time OS

RX78K/0 Notes 1, 2, 3, 4	78K/0 series real-time OS
MX78K0 Notes 1, 2, 3, 4	78K/0 series OS



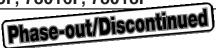


Fuzzy Inference Devleopment Support System

FE9000 Note 1/FE9200 Note 6	Fuzzy knowledge data creation tool	
FT9080 Note 1/FT9085 Note 2	Translator	
FI78K0 Notes 1, 2	Fuzzy inference module	
FD78K0 Notes 1, 2	Fuzzy inference debugger	

- Notes 1. PC-9800 series (MS-DOSTM) based
 - 2. IBM PC/AT and compatible (PC DOSTM/IBM DOSTM/MS-DOS) based
 - 3. HP9000 series 300^{TM} (HP-UXTM) based
 - 4. HP9000 series 700TM (HP-UX) based, SPARCstationTM (SunOSTM) based, EWS4800 series (EWS-UX/V) based
 - **5.** PC-9800 series (MS-DOS + WindowsTM) based
 - 6. IBM PC/AT and compatible (PC DOS/IBM DOS/MS-DOS + Windows) based
 - 7. NEWSTM (NEWS-OSTM) based
- Remarks 1. For development tools manufactured by a third party, refer to the 78K/0 Series Selection Guide (U11126E).
 - 2. RA78K/0, CC78K/0, SM78K0, ID78K0, SD78K/0, and RX78K/0 are used in combination with DF78014.





APPENDIX B. RELATED DOCUMENTS

Device Related Documents

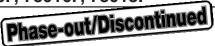
	Document Name		Document No.	
			Japanese	English
*	μPD78018F, 78018FY Subseries User's Manual		U10659J	U10659E
*	78K/0 Series User's Manual - Instruction		U12326J	IEU-1372
*	78K/0 Series Instruction Table		U10903J	_
*	78K/0 Series Instruction Set		U10904J	_
	μPD78018F Subseries Special Function Register Table		IEM-5594	_
	78K/0 Series Application Note	Fundamental (I)	IEA-715	IEA-1288
		Floating-Point Arithmetic Program	IEA-718	IEA-1289

Development Tools Documents (User's Manual) (1/2)

	Document Name		Document No.	
Document Name			Japanese	English
	RA78K Series Assembler Package	Operation	EEU-809	EEU-1399
		Language	EEU-815	EEU-1404
	RA78K Series Structured Assembler Preprocessor		EEU-817	EEU-1402
*	RA78K0 Assembler Package	Operation	U11802J	U11802E
		Assembly Language	U11801J	U11801E
		Structured Assembly Language	U11789J	U11789E
	CC78K Series C Compiler	Operation	EEU-656	EEU-1280
		Language	EEU-655	EEU-1284
*	CC78K0 C Compiler	Operation	U11517J	U11517E
		Language	U11518J	U11518E
	CC78K/0 C Compiler Application Note	Programming Know-how	EEA-618	EEA-1208
*	CC78K Series Library Source File		U12322J	_
*	PG-1500 PROM Programmer	G-1500 PROM Programmer		EEU-1335
	PG-1500 Controller PC-9800 Series (MS-DOS) Based		EEU-704	EEU-1291
	PG-1500 Controller IBM PC Series (PC DOS) Based		EEU-5008	U10540E
*	IE-78000-R		U11376J	U11376E
*	E-78000-R-A		U10057J	U10057E
	IE-78000-R-BK		EEU-867	EEU-1427
	IE-78014-R-EM-A		EEU-962	U10418E
	EP-78240		EEU-986	EEU-1513
	EP-78012GK-R		EEU-5012	EEU-1538
	SM78K0 System Simulator	Reference	U10181J	U10181E

Caution The contents of the above related documents are subject to change without notice. The latest documents should be used for designing, etc.





Development Tools Documents (User's Manual) (2/2)

	Document Name		Document No.	
	Document Name		Japanese	English
*	SM78K Series System Simulator	External Part User Open Interface Specifications	U10092J	U10092E
*	ID78K0 Integrated Debugger EWS Based	Reference	U11151J	_
*	ID78K0 Integrated Debugger PC Based	Reference	U11539J	U11539E
*	ID78K0 Integrated Debugger Windows Based	Guide	U11649J	U11649E
*	SD78K/0 Screen Debugger	Introduction	EEU-852	U10539E
	PC-9800 Series (MS-DOS) Based	Reference	U10952J	_
*	SD78K/0 Screen Debugger	Introduction	EEU-5024	EEU-1414
	IBM PC/AT (PC DOS) Based	Reference	U11279J	U11279E

Embedded Software Documents (User's Manual)

	Document Name		Docum	Document No.	
			Japanese	English	
*	78K/0 Series Real-Time OS	Fundamental	U11537J	U11537E	
		Installation	U11536J	U11536E	
*	78K/0 Series OS MX78K0	Fundamental	U12257J	_	
	Fuzzy Knowledge Data Creation Tool		EEU-829	EEU-1438	
	78K/0, 78K/II, 87AD Series		EEU-862	EEU-1444	
	Fuzzy Inference Development Support System - Translator				
	78K/0 Series Fuzzy Inference Development Suport System -		EEU-858	EEU-1441	
	Fuzzy Inference Module				
	78K/0 Series Fuzzy Inference Development Support System -		EEU-921	EEU-1458	
	Fuzzy Inference Debugger				

★ Other Documents

Document Name	Document No.	
Document Name	Japanese	English
IC Package Manual	C10943X	
Semiconductor Device Mounting Technology Manual	C11535J	C10535E
Quality Grades on NEC Semiconductor Device	C11531J	C11531E
NEC Semiconductor Device Reliability/Quality Control System	C10983J	C10983E
Electrostatic Discharge (ESD) Test	MEM-539	_
Guide to Quality Assurance for Semiconductor Device	C11893J	MEI-1202
Guide for Products Related to Microcomputer: Other Companies	U11416J	_

Caution The contents of the above related documents are subject to change without notice. The latest documents should be used for designing, etc.





NOTES FOR CMOS DEVICES-

1 PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note: Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

(2) HANDLING OF UNUSED INPUT PINS FOR CMOS

Note: No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS device behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

(3) STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note: Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.





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- Device availability
- Ordering information
- · Product release schedule
- · Availability of related technical literature
- Development environment specifications (for example, specifications for third-party tools and components, host computers, power plugs, AC supply voltages, and so forth)
- Network requirements

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Fax: 65-250-3583

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